DRAM Bender: An Extensible and Versatile FPGA-based Infrastructure to Easily Test State-of-the-art DRAM Chips

Ataberk Olgun[§] Hasan Hassan[§] A. Giray Yağlıkçı[§] Yahya Can Tuğrul[§†]
Lois Orosa[§⊙] Haocong Luo[§] Minesh Patel[§] Oğuz Ergin[†] Onur Mutlu[§]
[§]*ETH Zürich* [†]*TOBB ETÜ* [⊙]*Galician Supercomputing Center*

arXiv:2211.05838v5 [cs.AR] 12 Sep 2023

To understand and improve DRAM performance, reliability, security, and energy efficiency, prior works study characteristics of commodity DRAM chips. Unfortunately, state-of-the-art open source infrastructures capable of conducting such studies are obsolete, poorly supported, or difficult to use, or their inflexibility limits the types of studies they can conduct.

We propose DRAM Bender, a new FPGA-based infrastructure that enables experimental studies on state-of-the-art DRAM chips. DRAM Bender offers three key features at the same time. First, DRAM Bender enables directly interfacing with a DRAM chip through its low-level interface. This allows users to issue DRAM commands in arbitrary order and with finer-grained time intervals compared to other open source infrastructures. Second, DRAM Bender exposes easy-to-use C++ and Python programming interfaces, allowing users to quickly and easily develop different types of DRAM experiments. Third, DRAM Bender is easily extensible. The modular design of DRAM Bender allows extending it to (i) support existing and emerging DRAM interfaces, and (ii) run on new commercial or custom FPGA boards with little effort.

To demonstrate that DRAM Bender is a versatile infrastructure, we conduct three case studies, two of which lead to new observations about the DRAM RowHammer vulnerability. In particular, we show that data patterns supported by DRAM Bender uncover a larger set of bit-flips on a victim row than those commonly used by prior work. We demonstrate the extensibility of DRAM Bender by implementing it on five different FPGAs with DDR4 and DDR3 support. DRAM Bender is freely and openly available at `https://github.com/CMU-SAFARI/DRAM-Bender`.

1. Introduction

DRAM [73] is the dominant technology used in building the main memory of computer systems as it provides low access latency and can be manufactured at low cost per bit. Challenges in DRAM technology scaling render continuous improvement of DRAM performance, energy efficiency, security, and reliability difficult [255, 256].

To improve DRAM in all aspects and overcome DRAM scaling challenges, it is critical to experimentally understand the operation and characteristics of real DRAM chips. As such, it is critical to develop experimental testing infrastructures to efficiently and easily test real state-of-the-art DRAM chips. We refer to these infrastructures as DRAM testing infrastructures. These infrastructures enable at least two major possibilities.

Understanding DRAM Scaling Trends. Technology node scaling affects various DRAM characteristics, such as DRAM cell capacitance and capacitive crosstalk, negatively impacting the reliability, latency, and security characteristics of DRAM [172, 237, 255]. Therefore, it is important to thoroughly analyze these effects to understand how real DRAM chip characteristics change with technology scaling. Using DRAM testing infrastructures, prior studies uncover insights that inspire new mechanisms/methodologies for improving DRAM access latency [59, 60, 62, 66, 132, 190, 209-211, 331, 352], improving DRAM energy efficiency [63, 130, 225, 283, 294], understanding and mitigating the Rowhammer problem [193, 196, 256, 257, 277, 374], and understanding DRAM data retention failures [124, 180, 183, 224, 225, 283, 294, 347]. Such understanding is very difficult, if not impossible, to develop without testing real chips.

Uncovering Undocumented Functionality. Standard DRAM interfaces define constraints (e.g., timing parameters) that the memory controller obeys to guarantee correct DRAM operation. These constraints, by design, preclude the discovery of various undocumented operations that the DRAM technology or the chip design may inherently be capable of. For example, recent works demonstrate techniques that enable several in-DRAM computation primitives (e.g., bulk data copy [102, 270, 316], bitwise operations [102, 315, 317], true random number generation [27, 192, 272], and physical unclonable functions [27, 191, 276, 337]) using off-the-shelf DRAM devices by violating the DRAM timing parameters. Such undocumented DRAM behavior is possible to discover and demonstrate *only* by testing real DRAM chips using infrastructures that can violate DRAM timing parameters.

Limitations of Existing Infrastructures. DRAM timing parameters *cannot* be freely modified or violated in widely available computer systems. In such systems, the CPU sends memory requests (e.g., load/store) to the memory controller to access DRAM. The memory controller translates the memory request to appropriate low-level DRAM commands that strictly comply with the interface specification (i.e., DRAM standard) of the DRAM chip (i.e., the memory controller does *not* violate DRAM timing parameters). Thus, the two major research directions cannot be explored using typical computer systems as such exploration would require modifications to existing memory controllers.

To overcome the limitations of existing computer systems, prior works develop DRAM testing infrastructures that allow issuing DRAM commands with modified/violated timing parameters to DRAM chips. Unfortunately, the two existing FPGA-based open source DRAM testing infrastructures (SoftMC [134] and LiteX RowHammer Tester [17]) suffer from critical issues that prevent researchers from easily pursuing the above research directions. These infrastructures *(i)* do not

fully expose the DRAM interface to test programs (i.e., impose restrictions on the DRAM interface that limit studies that can be performed), *(ii)* are fairly difficult to use, or *(iii)* are difficult to extend to support new DRAM interfaces.

Interface Restrictions. Both SoftMC and Litex RowHammer Tester (LRT) expose a restricted view of the DRAM interface to test programs due to the limited capability provided by their instruction set architectures (ISA). First, SoftMC imposes restrictions on data patterns that can be used in initializing DRAM rows. Second, SoftMC imposes a non-deterministic delay in the order of microseconds between different parts of a DRAM test program. Third, LRT imposes 10 ns of delay between successive DRAM commands (i.e., a DRAM timing parameter can only be violated down to 10 ns and many standard DRAM timing parameters [158, 162, 163] *cannot* even be violated). These restrictions *limit* the types of experimental studies supported by both platforms.

Ease of Use. SoftMC and LRT are difficult to use. First, SoftMC *(i)* is only prototyped on a discontinued FPGA board, and *(ii)* has run-time dependencies that are obsolete and challenging to set up. Therefore, obtaining or setting up a system that readily supports SoftMC to conduct experimental studies is difficult. Second, LRT requires users to implement a new hardware module that post-processes experimental data read from DRAM (by using a hardware description language (HDL) such as Verilog) for every new type of experiment. Developing a hardware module is considerably difficult compared to developing a computer program for post-processing and requires expertise in HDL. As such, LRT *cannot* be easily used as a general DRAM testing infrastructure.

Extensibility. SoftMC *(i)* supports *only* DDR3 and has a hardware design that is not modular, and *(ii)* has a deprecated development environment that consists of outdated hardware design tools. Therefore, it *cannot* be easily modified to support DDR4 or other current and future DRAM interfaces.

Our goal is to develop an infrastructure that is superior to past infrastructures by overcoming their shortcomings. To this end, we design and develop DRAM Bender. DRAM Bender *(i)* fully exposes the DRAM interface to test programs through its nonrestrictive instruction set architecture, *(ii)* provides easy-to-use C++ and Python programming interfaces, and open source working prototypes of itself on five different modern FPGA boards, *(iii)* has a modular design and provides the necessary HW/SW components to facilitate the integration of new DRAM standards. Table 1 presents a qualitative comparison of DRAM Bender against the two other open source DRAM testing infrastructures available today.

Key Results. We *(i)* evaluate DRAM Bender's versatility in types of experimental studies on DRAM (Section 4), *(ii)* demonstrate DRAM Bender's ease of use (Sections 4.1 and 4.2), and *(iii)* evaluate DRAM Bender's extensibility to new DRAM interfaces (Section 3.4.2). First, leveraging DRAM Bender's *versatility* in conducting experimental studies on DRAM, we uncover two new insights into the RowHammer problem [196, 259] (Sections 4.1 and 4.2) and demonstrate that processing-using-memory capability (i.e., bulk bitwise execution capability) exists in real DDR4 chips (Section 4.3). Our results show that i) the effectiveness of a double-sided RowHammer attack at causing bit-flips highly depends on the order in which the two aggressor rows are activated and precharged, and ii) data patterns supported by DRAM Bender can uncover a larger set of bit-flips in a victim row compared to the data patterns commonly used by prior work. Second, we demonstrate DRAM Bender's *ease of use* by showing that it can be used to perform a RowHammer experiment in 12 lines of C++ code and a bulk bitwise AND/OR operation in just 3 lines of C++ code, in working prototypes of DRAM Bender on five different modern FPGA boards. Third, we demonstrate that DRAM Bender is easy to extend (Section 3.4.2). The required source code modifications to port DRAM Bender to another FPGA board with a different DRAM interface are small (only 230 lines of additional Verilog and 30 lines of additional C++ code).[1]

DRAM Bender was first developed in 2019. Since then, it has been used in many studies [97, 133, 193, 202, 233, 272, 277, 374, 375]. In this work, we aim to describe it in full, demonstrate its novel capabilities, and open source it so that it provides a useful research tool to the memory systems research and development community.

This paper makes the following contributions:

- We develop DRAM Bender, an FPGA-based open source DRAM testing infrastructure that overcomes the three major shortcomings of prior infrastructures. DRAM Bender *(i)* fully exposes the DRAM interface, *(ii)* is easy to use, and *(iii)* is easy to extend and modify. DRAM Bender is the only general open source testing infrastructure to easily test DDR4 chips today.
- We make two new observations on RowHammer-induced bit-flips, a major reliability, safety, and security problem in modern DRAM chips. These observations can be used to construct better RowHammer attacks and defenses.
- We demonstrate that contemporary off-the-shelf DDR4 devices are capable of performing in-DRAM bitwise Majority, AND, and OR operations.
- We demonstrate the *extensibility* of DRAM Bender by developing its prototypes for five FPGA boards, which have either DDR4 DIMM/SODIMM or DDR3 SODIMM slots.
- We open source DRAM Bender [302] to facilitate research on understanding the operation and characteristics of real

[1] On top of the initial implementation of DRAM Bender with DDR4 support that comprises approximately 3400 lines of Verilog and 2000 lines of C++ code.

Table 1: Comparison of DRAM Bender to the major existing open source DRAM testing infrastructures

Testing Infrastructure	Interface (IF) Restrictions	Ease of Use	Extensibility	Protocol Support	FPGA Support
SoftMC [134]	Data IF	✗	✗	DDR3	One Prototype
LiteX RowHammer Tester (LRT) [17]	Command & Data IF	✗	✓	DDR3/4, LPDDR4	Two Prototypes
DRAM Bender (this work)	**No Restrictions**	✓	✓	**DDR3/DDR4**	**Five Prototypes**

DRAM chips. We also open source [303, 304] two prior works, U-TRR [133] and QUAC-TRNG [272], as example works DRAM Bender has enabled.

2. Background and Motivation

We provide a concise background on DRAM organization, cell access, and timing parameters in this section. We refer the reader to many prior works for more detailed background on these subjects [60-63, 97, 108, 130-132, 134, 148, 176, 180-182, 190-193, 196-198, 209, 211, 212, 224, 225, 234, 252, 260, 261, 269, 276, 281-283, 294, 316-318, 320, 335, 352, 353, 388].

2.1. DRAM Organization

DRAM-based main memory is typically organized hierarchically, as depicted in Figure 1. A *memory controller* in the CPU is connected to a *DRAM module* over a *DRAM channel*. Each module on a DRAM channel comprises multiple *DRAM chips*, where a set of chips that operate concurrently is referred to as a *DRAM rank*. A DRAM chip is partitioned into multiple *DRAM banks* that operate independently. A collection of *DRAM cells*, *row decoders*, and *row buffers (sense amplifier arrays)* constitute a DRAM bank.

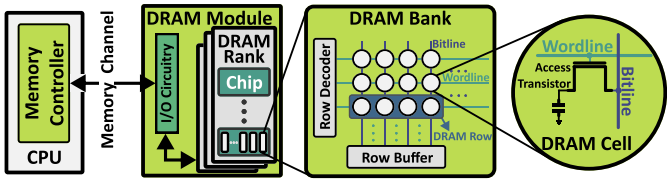


Figure 1: DRAM Organization

DRAM cells that are laid out onto the same *wordline* are accessed simultaneously, and referred to as a *row*. Each cell in a row is connected to a different *bitline* over an *access transistor*. A bitline connects one DRAM cell from each row to a sense amplifier in the row buffer. A DRAM cell stores data as charge in a capacitor. A sense amplifier can read or manipulate a DRAM cell's value by sampling or driving a bitline.

2.2. Accessing a DRAM Cell

Initially, the bitline is *precharged* to a reference voltage level ($V_{DD}/2$). The memory controller sends an `activate (ACT)` command to a *row* to enable the wordline. This starts the *charge-sharing* process, where the DRAM cell on the wordline shares its charge with its bitline. The sense amplifier samples the bitline voltage and detects a deviation towards V_{DD} or 0, depending on the value stored in the DRAM cell, and amplifies it. The DRAM cell can then be read or its value updated using `READ`/`WRITE` commands until the bank is finally `precharged (PRE)` to access another row.

2.3. DRAM Timing Parameters

Each DRAM standard defines a set of *timing parameters*. A timing parameter specifies the minimum time between two DRAM commands to guarantee correct operation. We describe two relevant timing parameters:

tRAS. Time window between an `ACT` and the next `PRE` command. During **tRAS**, charge of the DRAM cells on the open DRAM row is fully restored.

tRP. Time window between a `PRE` and the next `ACT` command. **tRP** is required for the open wordline to be closed and the DRAM bitlines be precharged to $V_{DD}/2$.

2.4. DDR PHY Interface (DFI)

A memory controller is typically composed of two modules: *(i)* the *scheduler* generates and schedules the corresponding DRAM commands to serve memory requests (e.g., load and store requests), *(ii)* the *PHY layer* manipulates the physical interface signals to transmit DRAM commands and data over the DRAM interface to the DRAM chips. The DDR PHY Interface (DFI) [76] standardizes the communication between the memory controller and the PHY layer, enhancing the reusability of memory controller designs.

DFI signals are broadly classified into *(i) control* signals that are used to issue DRAM commands, which are mostly analogous to the DRAM physical interface signals (e.g., `cas`, `ras`, and `we` signals), *(ii) read & write data* signals that are used to transfer data over the DRAM interface. These signals in the DFI fully expose the underlying physical DRAM interface to the memory controller. We refer the reader to the DFI Specification [76] for more details.

2.5. RowHammer

RowHammer, first introduced in 2014 [196], is a circuit-level phenomenon in DRAM devices, where frequent activation of an *aggressor* DRAM row induces bit-flips on DRAM cells in nearby *victim* rows. RowHammer is an important DRAM security/reliability/safety vulnerability that becomes more severe as DRAM devices scale to smaller technology nodes [193, 196, 277]. A *RowHammer attack* can flip critical bits in memory and can be used to escalate privilege and break confidentiality in real systems (as shown in, e.g., [2, 25, 33, 38, 39, 52-55, 57, 67-69, 71, 87, 88, 93, 96, 97, 115, 116, 133, 137, 150, 155, 156, 165, 174, 196, 200, 206, 216, 219, 222, 226, 254, 256, 258, 275, 287, 288, 291, 296, 297, 300, 305, 312, 313, 332, 338, 339, 342, 343, 345, 346, 351, 355, 359, 378, 379, 389, 391, 393, 395]).

2.6. FPGA-based DRAM Testing Infrastructures

SoftMC [134, 306] and Litex RowHammer Tester (LRT) [17] are the only two open source FPGA-based DRAM testing infrastructures that exist today.

SoftMC [134, 306] is an open source DDR3 testing infrastructure. SoftMC issues DDR3 command traces to the DDR3 device under test. A host machine transmits these command traces to the FPGA board that implements SoftMC.

Litex RowHammer Tester [17] is a RowHammer testing infrastructure that is primarily designed to conduct RowHammer experiments on DDR3/4 and LPDDR4 chips. LRT receives DRAM command sequences from the host machine and issues them to the DRAM device.

Both SoftMC and LRT suffer from multiple shortcomings that make them inadequate to satisfy the requirements of a versatile, easy-to-use, and extensible FPGA-based DRAM testing infrastructure. We describe these shortcomings in detail:

Shortcomings of SoftMC. First, SoftMC imposes restrictions on DDR3 data transfers. By replicating an 8-bit data pattern

provided by the user, SoftMC initializes DRAM cache blocks (512-bits) with repetitive data. This prevents its users from exploring the large search space of data patterns that can be used in experimental DRAM studies (Section 4.2). Second, due to its DDR3 command trace-based execution model, SoftMC imposes a non-deterministic delay on the order of a few microseconds between DDR3 command traces that are executed back-to-back. This prevents a user from running a class of experiments (e.g., energy measurements, Section 5.2) that require precise command timings over a long period of time (i.e., on the order of seconds or minutes, where SoftMC needs to execute multiple DRAM command sequences and induces multiple non-deterministic delays on the order of microseconds). Third, SoftMC is fairly difficult to use and extend. It is only prototyped on the ML605 FPGA board [365], which is no longer manufactured. SoftMC's development environment contains obsolete and discontinued software and hardware components [153, 366]. Fourth, SoftMC's DDR3 interface implementation is not decoupled from its remaining hardware via a well-defined interface (i.e., SoftMC is hard-coded to work with DDR3 modules). Thus, implementing new DRAM standards (e.g., DDR4) requires major intrusive modifications to SoftMC's hardware design.

Shortcomings of LRT. First, LRT does not support timing delays between successive DRAM commands smaller than 10 ns [223]. This greatly limits the DRAM experiment space supported by LRT. For example, many prior works that evaluate DRAM under reduced activation latency [60, 102, 190-192] and under greatly reduced $tRAS$-tRP [102, 272] could not conduct their experiments using LRT. Second, LRT can transfer data between the host machine and the FPGA board at only up to 1.9 Mb/s [18]. A slow communication channel between the host machine and the FPGA board can greatly slow down experiments, as DRAM experiments often require a large amount of data to be transferred to the host machine for analysis (Section 3.4.1). To alleviate the overheads of data transfer and enable practical testing times for RowHammer experiments, LRT implements a specialized hardware module for post-processing. However, it would be impractical to develop a specialized module for each type of DRAM experiment. Thus LRT is difficult to use as a general DRAM testing platform.

2.7. Motivation for DRAM Bender

None of the existing open source DRAM testing infrastructures can be used to easily and comprehensively test state-of-the-art, DDR4 DRAM chips. Therefore, it is essential to develop an open source, versatile, easy-to-use, and extensible DRAM testing infrastructure to enable experimental studies on new DRAM chips. Based on this requirement and our evaluation of the existing DRAM testing infrastructures, we define three key features that a DRAM testing infrastructure should provide.

Nonrestrictive Interface. A DRAM interface typically provides commands that can be used to access and manipulate DRAM cells (e.g., `READ` and `WRITE`), DRAM bank state (e.g., `ACT` a row), and device state (e.g., enter/exit self-refresh mode). To enable a rich DRAM testing environment, an infrastructure must provide a *nonrestrictive* application programmer interface (API) that *directly exposes* the DRAM interface to a test program. The API must not enforce any timing constraints nor any restrictions on the ordering of DRAM commands issued to the DRAM device.

Ease of Use. The infrastructure must be easy to *(i)* develop, for low-effort integration of new DRAM interfaces and prototyping on new FPGA boards, *(ii)* build, to easily bring up a working prototype using software and hardware tools that are widely available, and *(iii)* use, to seamlessly design and conduct DRAM experiments.

Extensibility. DRAM interfaces continue to evolve as new workloads emerge and DRAM technology scales. Therefore, a DRAM testing infrastructure must be easily extensible to support the new DRAM interfaces (e.g., HBM2 [164], DDR5 [163]) to perform experiments on the latest technology DRAM devices.

Existing DRAM testing infrastructures lack at least one of these features and cannot be used to easily test state-of-the-art DDR4 chips. Thus, there is a need for an infrastructure that provides all three features to stimulate future DRAM research.

3. DRAM Bender

DRAM Bender is an extensible, versatile, and easy-to-use FPGA-based DRAM testing infrastructure. It comprises key hardware components that facilitate the integration of new DRAM interfaces in a modular design and provides a nonrestrictive and easy-to-use application programmer interface (API) that directly exposes the DRAM interface to the user.

Figure 2 depicts the block diagram of DRAM Bender. An FPGA board that implements DRAM Bender is attached to the host machine over a high-speed interface (e.g., PCIe [364]). A key component of DRAM Bender is the *programmable core*, where the DRAM tests, organized as self-contained DRAM Bender programs, are executed. The programmable core implements the DRAM Bender ISA, which exposes key functionalities to form a DRAM test program.

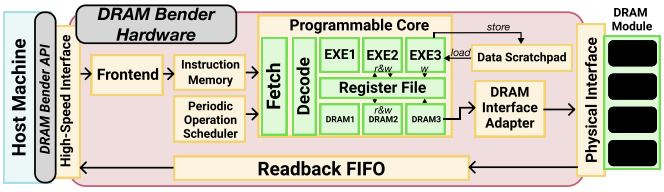


Figure 2: Block diagram of DRAM Bender

3.1. DRAM Bender ISA

The DRAM Bender ISA (Table 2) exposes key functionalities that the user needs to write a DRAM test program. For example, these functionalities include issuing DRAM command sequences with control flow (e.g., in a loop) and dynamically modifying the wide (e.g., 512-bits) data word that is written to DRAM with the execution of a `WRITE` command. There are two types of instructions in the DRAM Bender ISA: 1) RISC-like regular instructions that operate on the registers of the programmable core (e.g., arithmetic instructions and control-flow instructions), and 2) DRAM instructions that send DRAM commands to the DRAM module under test. A *DRAM*

instruction is composed of four[2] arbitrary DRAM commands. To fully expose the DRAM interface to the user, DRAM Bender permits arbitrary ordering of DRAM commands in a DRAM instruction.

Table 2: DRAM Bender ISA description

Type	Instruction	Description
MEM	LD	Load one word from the data scratchpad
	ST	Store one word to the data scratchpad
ARITH.	AND/OR/XOR	Bitwise AND/OR/XOR two registers
	ADD/SUB	Add/Sub two registers
	MV	Move a register's value to another register
	SRC	Cyclic shift a register to right
	LI	Load a register with an immediate value
CNTRL.	BL/BEQ	Branch if less than/equal
	JUMP	Jump to an address
	SLEEP	Stall for a number of cycles
MISC.	LDWD	Load the wide data register
	LDPC	Read a performance counter
	SRE/SRX	Self-refresh entry/exit
	END	Stop executing the program

Instruction Encoding. Figure 3 depicts the encoding of a subset of DRAM Bender ISA instructions. A DRAM command is encoded in 18 bits. The first two fields in a DRAM command specify the registers that store the address arguments of that DRAM command. For example, the first field of an ACT command indicates the *bank address* register and the second field indicates the *row address* register. The DRAM command encoding size determines the instruction size, and it is 72 bits.[3] We reserve 2 bits in the DRAM command encoding's op-code field to implement support for new commands in emerging and future DRAM interfaces (e.g., MPC in DDR5 [163]). We present a step-by-step guide on extending the ISA with new instructions on DRAM Bender's Github repository [302].

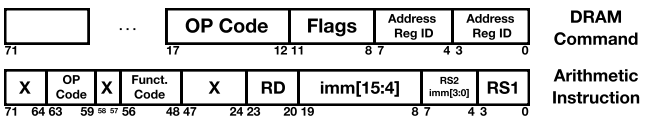


Figure 3: DRAM Bender instruction encodings

Registers. DRAM Bender implements 13 general purpose registers (GPRs) and four special registers. The first three special registers are called *address stride registers*. These registers determine by how much the *address registers* are automatically incremented with the execution of a DRAM instruction when the corresponding bit in the *flags* field is set. Automatically incrementing address registers allows DRAM Bender test programs to support a wide range of access patterns. For example, the user can tightly schedule `ACT` commands targeting different DRAM banks by automatically incrementing the bank address register value with each `ACT` command. The fourth special register is the *wide-data register*. This register is as large as the transfer size of the DRAM interface (e.g., 512 bits for an 8-chip DDR4 module [162]). The wide-data register can only be manipulated using the `LDWD` instruction, and is used by the `WRITE` command. The wide-data register allows users to initialize DRAM devices with arbitrary data patterns at the data transfer granularity (e.g., 512 bits in a DDR3/4 module). In contrast, a prior testing infrastructure [134] allows the users to *only* specify 8-bit data patterns, which are replicated 64 times to form the 512-bit transfer data, significantly limiting the data patterns that can be used in DRAM experiments (e.g., the prior testing infrastructure *cannot* randomly initialize DRAM chips).

3.2. DRAM Bender Hardware Modules

The hardware components of DRAM Bender are: *(i)* a specialized programmable core that implements the DRAM Bender ISA, *(ii)* a modular memory controller subsystem, and *(iii)* multiple memory elements that are used to store the DRAM Bender program and data, and buffer the data read back from the DRAM device under test.

3.2.1. Programmable Core. DRAM Bender comprises a programmable core that implements the DRAM Bender ISA. To enable the programmable core to achieve high frequencies that are required to interface with DRAM devices (under normal operating conditions, the minimum operating frequency for DDR4 devices is 666 MHz [162]), we design it as an in-order core with five pipeline stages: *(i) fetch*, *(ii) decode* and *(iii)* three *execute* stages. The fetch stage fetches a single instruction (72 bits) from the *instruction memory*. The decode stage decodes the instruction into either an *execute* micro-operation (μ-op) or into four *DRAM* μ-ops.[4] The execute stages are separated into two pipelines: *(i) execute* pipeline, which executes regular μ-ops, and *(ii) DRAM* pipeline, which executes four DRAM μ-ops per cycle.

DRAM μ-ops. Each DRAM μ-op corresponds to a DRAM command. To execute a DRAM μ-op, DRAM Bender first reads the GPRs to obtain the address operands (e.g., bank address of a `PRE` command) of the corresponding DRAM command and then issues the command to the DRAM device over the physical interface. The timing parameters of a DRAM command sequence are indirectly specified by either regular *SLEEP* instructions or DRAM *NOP* μ-ops.

Pipeline Dependencies. Both pipelines read from and write to the register file at the second execute stage to maintain a simple design. The only exception to this is *LOAD* instructions, which write to the register file at the third execute stage for

[2]Most FPGA DRAM PHY designs serialize multiple DRAM commands that they receive each cycle and issue the commands to the DRAM device one by one at a higher frequency. The PHY design we use (Section 3.4.1) can be configured to receive up to four DRAM commands each cycle. By executing four DRAM commands per cycle, DRAM Bender can be clocked at a four times slower frequency than the minimum clock frequency defined by a DRAM standard.

[3]$18 \times 4 = 72$, as there are four DRAM commands in a DRAM instruction.

[4]DRAM Bender needs to execute four DRAM commands to commit an instruction that encodes DRAM commands. To distinguish between what is executed by DRAM Bender's hardware (i.e., the four DRAM commands) and the instruction execution capability exposed to the user via DRAM Bender's ISA (i.e., the instruction that encodes four DRAM commands), we refer to what DRAM Bender's hardware executes as micro-operations (μ-ops). DRAM Bender decodes a DRAM Bender ISA instruction into one (in case of a regular instruction) or four μ-ops (in case of a DRAM instruction). A μ-op signal flows through pipeline stages with the necessary information (e.g., execution flags, register identifiers, and operands) to correctly execute its corresponding DRAM Bender ISA instruction.

better design timing closure during implementation. Control-flow instructions (i.e., branches) simply stall the pipeline until they are resolved at the third execute stage. Since the penalty of control-flow instructions is deterministic (six clock cycles), stalling the pipeline does not affect the user-specified timing parameters of the DRAM command sequences in an unpredictable way.

3.2.2. DRAM Interface Adapter. DRAM Bender implements the DRAM interface adapter, which acts as an intermediary between the DRAM pipeline and the physical DRAM interface. The DRAM pipeline simply outputs a *one-hot encoded signal* for each DRAM command in a DRAM instruction. For example, a DRAM instruction with an `ACT` as its first and a `WRITE` as its third command would set the least-significant bit of the `dram_act` signal to "logic-1" and the third least-significant bit of the `dram_write` signal to "logic-1", while leaving all other signals at "logic-0". These signals are picked up by the *DRAM adapter* module, which essentially translates from this simplified interface (one-hot encoded signals) to a more complex PHY interface. The adapter is decoupled from the rest of the design such that it can be easily modified to integrate new DRAM interfaces.

Developers can easily extend DRAM Bender to support another DRAM interface by *(i)* defining new one-hot encoded signals that are set with the execution of new DRAM commands introduced in the new interface and *(ii)* modifying the adapter to match with the new DRAM PHY interface.

3.2.3. Memory Elements. DRAM Bender comprises multiple memory elements that store programs, program data, and data read back from DRAM during an experiment. The *instruction memory* stores the DRAM Bender program and it is initialized by the *frontend* module, which receives data over the high-speed interface (e.g., PCIe) from a host machine. The *data scratchpad* stores program data and it can be accessed and manipulated using `LD` and `ST` instructions.

3.2.4. Periodic Operation Scheduler. To maintain correct operation on the DRAM interface, DRAM devices typically need to receive a set of commands periodically.[5] The *periodic operations scheduler (POS)* performs these operations either with predefined (periodic `READ`, `ZQS`) or configurable (periodic refresh) periods. POS stores three DRAM Bender programs in its memory to conduct periodic `READ`, `ZQS` calibration, and refresh operations. It arbitrates between these programs to correctly schedule the required periodic operation to the DRAM device.

3.2.5. Readback FIFO. Typically, there is a discrepancy between the bandwidth of the high-speed host-FPGA interface and the DRAM interface on FPGA boards because the DRAM interface can be clocked at higher speeds. To alleviate the negative effects (e.g., pipeline stalls) due to this discrepancy on experiments conducted using DRAM Bender, we buffer the data read back from the DRAM device in a FIFO. The *readback FIFO* buffers data read from the DRAM device as it is sent to the host machine over the high-speed interface.

[5]For example, to compensate for voltage and temperature changes (ZQ Calibration [162]) and refresh leaky DRAM cells (DRAM Refresh).

Avoiding Readback Stalls. The readback FIFO may fill up during the execution of a DRAM Bender program, in which case the host machine must read the FIFO to allow the upcoming `READ` commands to execute. DRAM Bender adopts a preemptive mechanism to stall programs at a timing-non-critical point (i.e., while executing regular instructions) to prevent the user-specified timing parameters of DRAM command sequences from being violated. In other words, DRAM Bender *never* stalls a program while executing a continuous sequence of DRAM commands.

DRAM Bender stalls a program prior to the execution of a continuous DRAM command sequence that contains `READ` commands (DRAM command sequences without a `READ` command do *not* cause readback stalls). The API automatically inserts into DRAM Bender programs hints which specify the number of `READ` commands that will be executed in the next continuous DRAM command sequence. DRAM Bender lets such command sequences execute *only* if there is enough space within the readback FIFO, and stalls them otherwise.

3.3. DRAM Bender Software Modules

DRAM Bender contains two major software modules: *(i)* the application programmer interface, and *(ii)* program debugger.

3.3.1. Application Programmer Interface (API). DRAM Bender provides an easy-to-use and nonrestrictive application programmer interface (API) implemented in C++. This API is *extensible* with a modular design that allows developers to easily integrate new DRAM interfaces to DRAM Bender, and adapt DRAM Bender to new FPGA boards. The API is composed of three components: *(i)* the `program` class defines how DRAM Bender programs are created, *(ii)* the `platform` class exposes the FPGA-based platform to the user via key functions, *(iii)* the `board` class implements wrapper functions that communicate with the FPGA board over that FPGA board's interface (e.g., PCIe drivers). DRAM Bender also implements a `Python` interface that provides the same functionality as the C++ API using `pybind11` [290]. The `Python` interface allows 1) agile development and verification of DRAM Bender programs, and 2) simple workflow for easy integration of popular data analysis and visualization frameworks (e.g., [341, 354]). We describe the two components in the API in more detail.

Program. The `program` class encapsulates functions that are used to create DRAM Bender programs. A DRAM Bender program is internally represented as a list of instructions by the API. The user constructs this list by appending instructions to the list one by one. Users can also append labels to a program which can be used as branch targets of control-flow instructions. This convention allows the user to easily create DRAM Bender programs. To demonstrate the ease of use, Listing 1 depicts a C++ code example that uses the DRAM Bender API to create a DRAM Bender program that reads from a DRAM row. Our open source repository [302] contains other C++ code examples (e.g., for characterizing data retention time) that the users can benefit from or build upon.

```
1  // The program below reads all cells in Bank 0, Row 0
2  // R5: bank address, R4: row address, R3: column address
3  // CASR: column stride register, R6: last column to read
4  Program p; // A sequentially-generated instruction list
5  p.appendLI(R5, 0); // Add a new instruction to the list
6  p.appendLI(R4, 0);
7  p.appendLI(R3, 0);
8  p.appendLI(CASR, 8); // Column address will increase by 8
9  p.appendLI(R6, 1024); // Read until 1024th column address
10 p.appendACT(R5, false, R4, false, 11);
11 p.appendLabel("read");
12 p.appendREAD(R5, false, R3, true, false, false, 0);
13 p.appendBL("read", R3, R6);
14 p.appendPRE(R5, false, false, 0);
```

Listing 1: Example DRAM Bender program that reads a row

The `program` class defines a set of functions that are based on the template `append<Instruction>`. Each `append` function either inserts a regular instruction or a DRAM command into the program. `append` functions that insert regular instructions have RISC-like argument orderings, e.g., `appendLI(R5, 0)` (line 5) inserts a load immediate instruction that sets the value of R5 to 0. The arguments of `append` functions that insert DRAM commands into the program (lines 10, 12, and 14) are ordered as *(i)* address register identifier (one or two), *(ii)* address register increment flag (one or two), *(iii)* other flags, and *(iv)* an optional delay (highlighted in red in Listing 1).

Using the optional delay, users can easily create DRAM command sequences with arbitrary timing parameters. The address register increment flag allows for access patterns with arbitrary strides. As an example, the arguments of the `appendACT` function (line 10) in listing 1 are *(i)* **R5**, bank address register (BAR), *(ii)* **false**, *do not* increment BAR by bank address stride register, *(iii)* **R4**, row address register (RAR), *(iv)* **false**, *do not* increment RAR by row address stride register, and *(v)* wait for **11** additional DRAM command bus cycles after issuing the `ACT` command, in order from left to right. In the `appendREAD` function, the user reads all DRAM cache blocks in a DRAM row by setting the column address register increment flag, without having to execute `ADD` instructions inbetween `READ` commands. This allows the user to schedule DRAM commands with as tight timing delays as possible.

Platform. The `platform` class defines methods to *(i)* execute programs on the infrastructure, *(ii)* manipulate the state of the platform (e.g., reset, enable auto-refresh), and *(iii)* retrieve data from the platform over the high-speed interface.

Board. The `board` class defines how data is transferred between the host machine and the FPGA infrastructure over the high-speed interface. It exposes two key functions to the platform class, `sendData` and `receiveData`, which are overloaded by the code that implements the FPGA board-specific interface (e.g., Xilinx XDMA [369]). `sendData` is used by the platform class to send a program to the FPGA, and `receiveData` is used to read data back from the DRAM device under test.

3.3.2. Program Debugger. DRAM Bender provides an easy-to-use program debugger. The debugger is used to analyze and debug DRAM Bender programs generated by the API without access to the hardware setup. It uses the Vivado Simulator [367] to run timing-critical simulations of the hardware setup, which includes a DRAM device model. Using the DRAM model, the debugger can inform the user of every timing violation, which enables the user to easily understand if their program runs correctly (i.e., it does not violate DRAM timing parameters unexpectedly). The tight integration of the debugger and the Vivado Simulator allows users to view waveform diagrams and select which hardware signals to debug conveniently, using Vivado's graphical user interface.

3.4. DRAM Bender Prototypes

We implement DRAM Bender on five different FPGA boards that support different DRAM standards (DDR3, DDR4) and DRAM modules with different form factors (SODIMM, RDIMM, UDIMM), to demonstrate the extensibility of DRAM Bender. Among these five prototypes, we highlight the Xilinx Alveo U200 board prototype. When augmented with a SODIMM to DIMM adapter (e.g., JET-5608AA [168]), this prototype can be used to test a large majority of all available DRAM modules.[6] Different modules can contain DRAM chips built using different packaging technologies (e.g., FBGA 78 and FBGA 96). A DRAM Bender user can find out what packaging technologies are used in chips on a DRAM module by inspecting the relevant module manufacturer specifications. Therefore, a DRAM Bender user can test different DRAM packages. Table 3 describes the details of DRAM Bender prototypes on different boards. Table 4 shows the FPGA resource utilization for each DRAM Bender prototype.

In all prototypes, the *instruction memory* stores *2048 instructions*, the *scratchpad* stores *1024 words (32-bits)*, and the *read-back FIFO* is *32 KiB* (i.e., buffers up to 512 DRAM data transfers). DRAM Bender supports a DRAM timing resolution (i.e., the minimum distance between two consecutive DRAM commands) of 1.5 ns in DDR4 boards and a DRAM timing resolution of 2.5 ns in the DDR3 board.[7]

Table 3: DRAM Bender FPGA prototypes

FPGA Board	DRAM Standard	Module Form Factor
Xilinx Alveo U200 [371]	DDR4	[U/R/SO]DIMM
Bittware XUSP3S [42]	DDR4	SODIMM
Bittware XUPP3R [40]	DDR4	RDIMM
Bittware XUPVVH [41]	DDR4	RDIMM
Xilinx ZC706 [362]	DDR3	SODIMM

Controlled Environment. To conduct experiments in a controlled environment, our infrastructure incorporates a programmable Maxwell FT200 [242] temperature controller (Figure 4a) connected to silicone rubber heaters attached to both sides of the DRAM module (Figure 4b). To measure the actual temperature of DRAM chips, we use a thermocouple, which we place between the rubber heaters and the DRAM chips. We connect the heater pads and the thermocouple to the temperature

[6] More details are in our GitHub repository [302] including a pictorial depiction of how the SODIMM to DIMM adapter is used with the Xilinx Alveo U200 board prototype to test SODIMMs.

[7] We configure our prototypes such that the DRAM interface operates at the minimum standard frequency. This allows for DRAM Bender's hardware to satisfy the tight FPGA timing constraints in a subset of the FPGA boards (Bittware XUSP3S and Xilinx ZC706) with fairly old and resource-bound FPGAs. When necessary, DRAM Bender can be implemented on other FPGA boards with newer FPGAs to satisfy a finer timing resolution out of the box (e.g., at least as fine as 1.25 ns in Bittware XUPVVH [41]).

Table 4: DRAM Bender FPGA resource utilization

Resource	XUSP3S	XUPP3R	XUPVVH	U200	ZC706
LUT	6.59%	3.25%	2.94%	3.01%	7.90%
LUTRAM	2.55%	0.34%	0.34%	0.34%	1.68%
FF	3.46%	1.80%	1.69%	1.78%	3.08%
BRAM	5.21%	4.75%	4.99%	4.61%	8.17%
DSP	0.39%	0.04%	0.03%	0.04%	0.00%
IO	17.09%	17.09%	23.24%	18.34%	32.60%
GT	12.50%	10.53%	8.33%	33.33%	25.00%
BUFG	1.25%	1.17%	1.98%	1.11%	28.13%
MMCM	6.25%	3.33%	8.33%	3.33%	25.00%
PLL	9.38%	5.00%	12.50%	5.00%	12.50%
PCIe	25.00%	16.67%	16.67%	16.67%	100.00%

controller. The temperature controller keeps the temperature stable via implementing a closed-loop PID controller.[8]

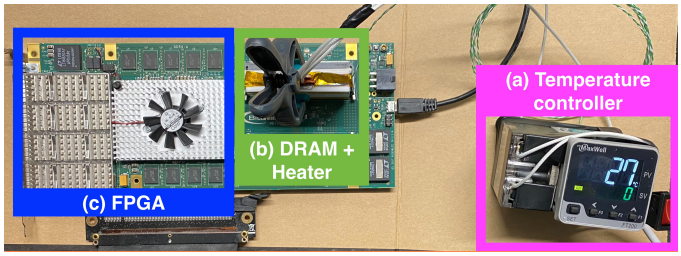


Figure 4: DRAM Bender Hardware Infrastructure

Temperature Measurement Stability. We conduct a temperature controller stability experiment to demonstrate that the temperature we measure using our setup is stable and remains close to the target temperature throughout a day. First, we set the target temperature to 80.0 °C in three different prototypes (one of which is shown in Figure 4).[9] Second, we wait for the temperature to stabilize. Third, we record the temperature measurements every 5 seconds for 24 hours. We observe that the maximum variation in temperature is 0.2 °C (i.e., the highest recorded temperature is 80.2 °C and the lowest recorded temperature is 79.8 °C). Table 5 shows the proportion of temperature measurements that correspond to 80.2 °C, 80.1 °C, 80.0 °C, 79.9 °C, and 79.8 °C among all measurements.

Table 5: Observed temperature measurements when the target temperature is set to 80.0 °C in three different prototypes.

Measured Temperature (°C)	Proportion of measurements (%)		
	Prototype 1	Prototype 2	Prototype 3
80.2	0.07	0.02	0.01
80.1	11.73	5.20	7.58
80.0	77.34	88.96	86.28
79.9	10.13	5.81	6.08
79.8	0.74	0.02	0.05

Figure 5 depicts the measurements pictorially. We conclude that our infrastructure enables stable temperature control.

3.4.1. Hardware IP Cores. We make use of several Xilinx IP components across our prototypes.

Xilinx XDMA PCIe Engine. DRAM experiments can result in terabytes of data that is analyzed by the user program that runs on the host machine. Therefore, it is important to provide a high-speed host machine ↔ FPGA board interface. We implement PCIe as the high-speed interface in our prototypes as it has high throughput (several Gb/s [286]) and it is widely available among popular FPGA boards. We use the Xilinx DMA/Bridge Subsystem for PCIe Express IP [369] to communicate with the host machine over the PCIe interface. The IP is responsible for bringing up the PCIe connection with the attached host machine, and driving the physical PCIe signals with the data it receives from DRAM Bender hardware (data read from DRAM using `READ` commands) over the standard AXI4-Stream interface [21].

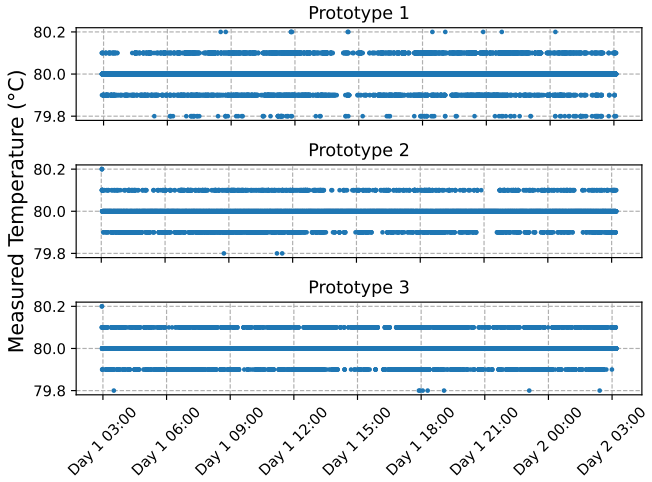


Figure 5: Observed temperature measurements when the target temperature is set to 80.0 °C in three different prototypes.

Xilinx DDR3/4 PHY. We issue DRAM commands to the Xilinx DDR3/4 PHY IP [370] over a low-level DFI interface. The IP receives multiple DRAM commands per FPGA clock cycle and performs the required operations to drive the physical DRAM interface signals (e.g., DQ, DQS) at high speeds, such as serializing multiple DRAM commands it receives to a higher frequency domain (e.g., the DDRx interface). By default, the IP imposes a constraint on the ordering of DDRx `READ` and `WRITE` commands. We modify the IP's Verilog source to remove this constraint.

FPGA designs typically use a DFI-like interface with a manufacturer-provided IP to communicate with memory devices [146, 361]. DRAM Bender can be easily adapted to support other memory standards by interfacing with manufacturer-provided IPs built for these memory standards (e.g., HBM2 [368], RLDRAM [145]). In fact, a recent work [271] adapts DRAM Bender to interface with modern HBM2 chips.

The IPs we use in our prototypes implement standardized interfaces to communicate with the DRAM Bender hardware. DRAM Bender can be relatively easily ported to new prototypes that use different IP (e.g., open source IP), given that they use the same common standard interfaces, e.g., AXI4, PHY interface. In particular, Intel provides a PCIe IP [147] and an external memory interface IP [146] for developers to use in their Intel FPGA designs. These IPs expose hardware interfaces similar to Xilinx's PCIe and DDR3/4 PHY IPs.

[8] In our experiments, we typically use the temperature range of [30 °C, 85 °C]. Based on the data sheets [242, 301] of the temperature controller and the sensor, we expect the maximum error in temperature measurements to be within ±1.11 °C.

[9] We use one Bittware XUSP3S (Prototype 1) and two Xilinx Alveo U200 (Prototype 2 and 3) FPGA prototypes.

3.4.2. DDR3 Changes. To show that DRAM Bender can be easily extended to support other DRAM interfaces and FPGA boards, we summarize the changes required for DRAM Bender to support DDR3 using the Xilinx ZC706 board [362]. First, we modify the *DRAM interface adapter* (Section 3.2.2) to correctly translate from DRAM pipeline signals to Xilinx DDR3 PHY [363] signals. Second, The PCIe connection is 0.6× slower in the ZC706 board (5.0 GT/s) compared to the other boards we use for DDR4 (8.0 GT/s). As a consequence, the AXI interface between the frontend and the Xilinx XDMA IP has a twice as narrow (128-bit) data bus. We make small modifications to the *frontend* module (Section 3.2.3) to account for this change in the data bus. Third, we slightly modify the `sendData` function in the API to correctly partition instructions into packets sent over the PCIe bus. Overall, our changes introduce only **230** additional lines of Verilog code in the hardware description and **30** additional lines of C++ code in the API. Our Github repository includes all ZC706 DDR3 design sources [302].

3.5. Experiment Workflow

To show how instructions and data flow between DRAM Bender components during an experiment, we describe a typical experiment workflow when using the DRAM Bender infrastructure. Figure 6 summarizes the workflow.

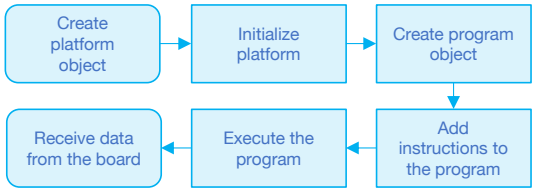


Figure 6: DRAM Bender experiment workflow

The user 1) creates a platform object, 2) initializes the DRAM Bender platform using the `platform.initialize()` function, 3) creates a program object, 4) adds instructions to the program object using `append<Instruction>` functions, 5) programs DRAM Bender by supplying the program object to the `platform.execute()` function, and 6) retrieves data from the FPGA board by using the `platform.receiveData()` function to analyze output data.

4. Use Cases

To demonstrate that DRAM Bender is a versatile DRAM testing infrastructure, we conduct three new case studies that result in new observations: *(i)* we investigate the effects of the order in which the two aggressor rows are activated and precharged (i.e., the interleaving pattern of activations to the aggressor rows) on RowHammer [196, 262], *(ii)* we investigate the effects of data patterns on RowHammer and show that DRAM Bender can be used to uncover new insights into the RowHammer vulnerability, and *(iii)* we demonstrate for the first time that processing-using-memory capability exists in off-the-shelf DDR4 chips. The source code for all three case studies is available on our Github repository [302].

Experimental Setup. In all case studies, we use Alveo U200 [371] boards that are set up as described in Section 3.4. We keep the temperature of the DRAM chips that we test at 50 °C. We disable all DRAM self-regulation events (e.g., DRAM Refresh [162]) to *(i)* minimize all possible sources of interference [193], and *(ii)* disable proprietary in-DRAM RowHammer protection mechanisms (e.g., Target Row Refresh [97, 133]). We disable all forms of rank-level error-correction codes (ECC) to make sure ECC does not obscure RowHammer-induced bit-flips. Table 6 lists the DRAM modules from three different manufacturers that we use in our experiments. We test one memory module (8 DRAM chips) from each manufacturer.

4.1. Study #1: RowHammer: Interleaving Pattern of Activations

To demonstrate DRAM Bender's ease of use for developing new experiments that uncover new insights, we conduct a comprehensive experiment to study the effects of the interleaving pattern of activations to the aggressor rows on RowHammer bit-flips. Figure 7 depicts the double-sided RowHammer attack [193, 196, 277, 313] in our case study. We pick five consecutive rows V1, A1, V2, A2, V3, and rapidly activate the aggressor rows (A1 and A2) and record the bit-flips observed in the victim rows (V1, V2 and V3). The interleaving pattern describes how many times one aggressor row is hammered before switching to the hammering of the other aggressor row in one iteration of the attack.

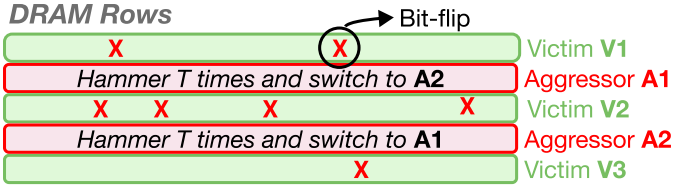


Figure 7: Double-sided RowHammer attack

Methodology. We use the checkered data pattern as it is reported to have the highest average RowHammer error coverage across DDR4 modules from three manufacturers in [193]. This data pattern initializes aggressor rows A1 and A2 (see Figure 7) with "0xAA" values and victim rows V1, V2, and V3 with "0x55" values. We activate aggressors in an interleaved manner. In each iteration, we 1) activate the first aggressor row T times, and 2) activate the second aggressor row T times. We sweep the value of T and observe the number of bit-flips in the victim rows. We issue a total number of 1M ACT commands regardless of the value of T (e.g., the attack finishes in 8 iterations if $T = 64K$ and in 512K iterations if $T = 1$). We create a double-sided RowHammer attack program using the DRAM Bender API. Listing 2 depicts the key code portion that performs an iteration of the attack, which we repeatedly perform until we issue 1M ACT commands. We sweep T through the range [1, 64K], incrementing by a power of two after each iteration (i.e., we set T to 1, 2, 4, ..., 64K) to perform the double-sided RowHammer attack in a sequential ($T = 1$), and in a cascaded manner ($T > 1$).

Table 6: DRAM modules tested in all three case studies

Manufacturer	Module Part Number	Chip Part Number	Standard	Chip Density	Org.
Micron (A)	MTA18ASF2G72PZ-2G3B1QG	MT40A2G4WE-083E:B	DDR4 RDIMM	8Gb	1R×4
Hynix (B)	KVR24R17S8/4	H5AN4G8NAFR-UHC	DDR4 RDIMM	4Gb	1R×8
Samsung (C)	F4-2400C17S-8GNT	K4A4G085WF-BCTD	DDR4 UDIMM	4Gb	2R×8

```
1  p.appendLI(hammerCount, 0);
2  p.appendLabel("HAMMER1");
3  p.appendACT(bank, false, A1, false, tRAS);
4  p.appendPRE(bank, false, false, tRP);
5  p.appendADDI(hammerCount, hammerCount, 1);
6  p.appendBL(hammerCount, T, "HAMMER1");
7  p.appendLI(hammerCount, 0);
8  p.appendLabel("HAMMER2");
9  p.appendACT(bank, false, A2, false, tRAS);
10 p.appendPRE(bank, false, false, tRP);
11 p.appendADDI(hammerCount, hammerCount, 1);
12 p.appendBL(hammerCount, T, "HAMMER2");
```

Listing 2: DRAM Bender program that performs an iteration of the double-sided RowHammer attack

We use two metrics to demonstrate the effects of the interleaving pattern of activations in a RowHammer attack: *(i) average bit-flips per row* is the number of bit-flips in a DRAM bank averaged across all DRAM rows, *(ii)* HC_{first} is the number of ACT commands issued per aggressor row in a RowHammer attack to induce the first bit-flip in a particular DRAM row.

Results. Figures 8 and 9 show the number of bit-flips we observe in different modules as we sweep T from 1 to 64K.[10] Each bar represents the number of bit-flips we observe in one victim row (e.g., gold bar is the sandwiched row, V2) normalized to the number of bit-flips we observe in the same row at $T = 64K$, for all rows in a DRAM bank.

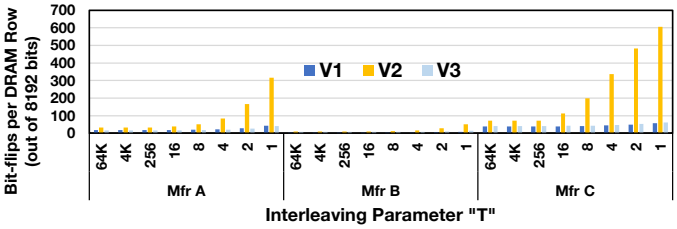


Figure 8: Effect of the interleaving pattern on bit-flip rate, as dictated by parameter "T"

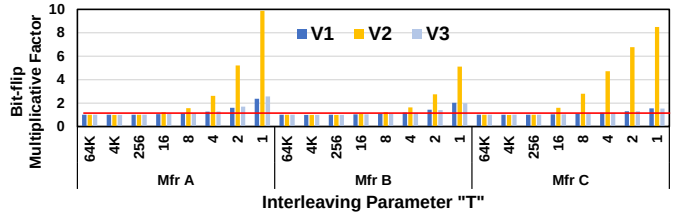


Figure 9: Effect of the interleaving pattern on bit-flip rate, as dictated by parameter "T" (normalized to $T = 64K$)

We make two new observations from Figure 9. First, the number of bit-flips in the sandwiched row (V2) significantly increases as T approaches one. Since the total number of ACT commands we issue (i.e., hammer count) remains the same, this observation suggests that the interleaving pattern of the ACT commands to the two aggressor rows in a double-sided RowHammer attack greatly affects the effectiveness of the attack. We observe on average across all double-sided victim (V2) rows (31.9, 9.9, 71.2) bit-flips at $T = 64K$, and (314.8, 50.7, 604.9) bit-flips at $T = 1$ for manufacturers (A, B, C) respectively. The double-sided RowHammer attack more strongly resembles a single-sided attack as T increases. Prior works (e.g., [24, 313]) show that single-sided attacks are less effective in inducing RowHammer bit-flips than double-sided attacks, and this could explain why our attack's effectiveness degrades as T increases.

Second, we observe that the number of bit-flips induced in the nearby victim rows, V1 and V3, also increases as T approaches one. We hypothesize that a combination of two phenomena explains this second observation: *(i)* V1 and V3 become less susceptible to RowHammer-induced bit-flips as their immediate neighbor aggressor row is hammered in a cascaded manner (i.e., T approaches 64K). A cascaded activation pattern causes the aggressor row to stay precharged for a longer time (one aggressor stays precharged while the other aggressor is being hammered). This might reduce the overall electron injection rate between the aggressor and victim rows [106, 350] and thus the RowHammer vulnerability of the victim row. *(ii)* The RowHammer blast radius effect [196], in which an aggressor row can induce bit-flips in victim rows that are not its immediate neighbors (e.g., A2 and V1), is strengthened as the attack alternates between aggressor rows more frequently (i.e., T approaches one).

Figures 10 and 11 show the number of ACT commands that is required to observe the first RowHammer bit-flip (HC_{first}) in the sandwiched DRAM row (V2) for each DRAM manufacturer using different values of T. For each T, we find the row with the smallest HC_{first} in a DRAM bank. We observe an HC_{first} of 99K, 80K, 16K at $T = 1$, and 130K, 108K, 23K at $T = 64K$ for manufacturers A, B, C, respectively. Hence, the interleaving pattern of the double-sided RowHammer attack affects the HC_{first} of a DRAM row. As the attack's interleaving pattern becomes more cascaded (i.e., T approaches 64K), HC_{first} increases. RowHammer defense mechanisms (e.g., [10, 19, 20, 24, 28-31, 34, 53, 75, 77, 86, 86, 89, 94, 95, 97, 114, 119, 120, 127, 131, 133, 136, 138, 149, 166, 167, 169, 170, 184, 194-196, 201, 213, 214, 217, 231, 232, 239-241, 262, 267, 279, 280, 295, 307, 309-311, 321, 323, 330, 344, 346, 348, 356, 357, 373, 375, 376, 381, 390, 392, 396]) may leverage this observation to render double-sided RowHammer attacks less effective by scheduling the aggressor row accesses in a cascaded manner to the DRAM module.

Conclusion. Based on our new observations enabled by DRAM Bender, we conclude that the interleaving pattern of the aggressor row activations in a double-sided RowHammer attack significantly affects 1) the number of RowHammer-induced bit-flips, and 2) the number of ACT commands re-

[10] To crisply demonstrate the trends, we leave out some of the T values from the plot. The trend we observe across those follow the trend in the figure.

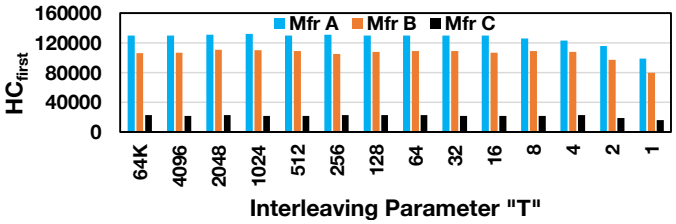


Figure 10: Effect of the interleaving pattern on HC_{first}, as dictated by parameter "T"

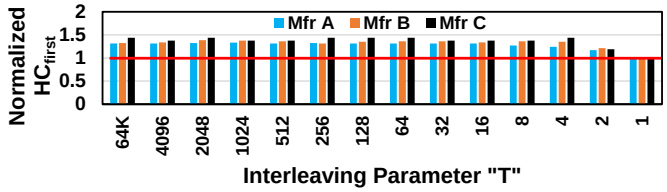


Figure 11: Effect of the interleaving pattern on HC_{first}, as dictated by parameter "T" (normalized to $T = 1$)

quired to induce the first RowHammer-induced bit-flip in a DRAM bank.

4.2. Study #2: RowHammer: Data Patterns

To demonstrate that DRAM Bender's nonrestrictive data interface is useful for generating new insights, we conduct a comprehensive experiment to study the effect of data patterns on RowHammer-induced bit-flips.

Methodology. We run a DRAM Bender test where we perform a double-sided RowHammer attack on a victim row and observe the bit-flips that occur in a DRAM cache block (512 bits) in the victim row. Our test code *(i)* initializes the aggressor rows using either 1) a *SoftMC* or 2) a *DRAM Bender data pattern*, *(ii)* conducts double-sided RowHammer on the victim row, *(iii)* records the positions of the bits that flip in one cache block in the victim row. We run two variations of the test code to observe the bit-flips induced by 1) SoftMC data patterns and 2) DRAM Bender data patterns. First, we use the limited 256 8-bit data patterns supported by SoftMC, used in many prior works to conduct Rowhammer experiments [133, 193, 196, 233, 275, 277]. Second, we use the 256 randomly-generated 512-bit DRAM Bender data patterns. We run the test code 100 times and aggregate all bit-flips across the 100 runs of the experiment to collect the complete set of RowHammer failures (e.g., a bit-flip that occurs at least once during the 100 rounds of testing is recorded as a bit-flip). We test 24 randomly selected DRAM cache blocks in 24 DRAM rows from each DRAM module to maintain a reasonable testing time. We repeat each test code variation twice, once by initializing the victim row with an all-zeros and once by initializing the victim row with an all-ones data pattern, to cover cells that flip from $1 - 0$ and $0 - 1$.

Results. We identify at least one additional cell that flips from either $1 - 0$ or $0 - 1$ when we initialize the aggressor rows with random 512-bit data patterns compared to when we initialize the aggressor rows with SoftMC data patterns on every victim row that we test in modules from all three DRAM manufacturers. We conclude that DRAM Bender can identify RowHammer-susceptible DRAM cells that cannot be identified using the SoftMC data patterns used in prior work. This information could be useful for strengthening RowHammer attacks that need to induce bit-flips in a particular cell [206].

4.3. Study #3: In-DRAM Bitwise Operations

Recent works propose processing-using-memory (PIM) techniques that can greatly improve system performance and reduce energy consumption [3, 7-9, 11-16, 22, 23, 26, 32, 36, 37, 44-51, 56, 62, 64, 65, 70, 72, 74, 78-80, 83-85, 90-92, 98, 99, 101-105, 107, 109-113, 117, 118, 121, 122, 125, 126, 128, 129, 135, 140, 141, 143, 144, 152, 154, 171, 173, 175, 185-189, 199, 203-205, 207, 208, 215, 218, 220, 221, 227-230, 236, 238, 250, 253, 255, 263-266, 272-274, 278, 284, 285, 289, 298, 299, 308, 314-317, 319, 322, 324-329, 334, 336, 353, 358, 360, 372, 380, 383-385, 387, 394, 397-399]. A recent work demonstrates that bitwise AND/OR operations can be performed in off-the-shelf DDR3 chips [102]. However, it is unclear if commonly-used newer-generation off-the-shelf DDR4 chips support these operations. Our goal in this section is to leverage DRAM Bender's support for fine-grained control over DRAM timing parameters and demonstrate that bitwise AND/OR operations can also be performed in off-the-shelf DDR4 chips. In our experiments, we perform bitwise operations by issuing a sequence of `ACT`→ `PRE`→ `ACT` commands with violated timing parameters. We characterize our DRAM modules to obtain the bit error rate (i.e., the fraction of bitlines that *cannot* correctly perform the bitwise operation) of the performed bitwise operations.

Majority Operation. To perform bitwise AND/OR operations, we use the *majority* function across DRAM cells on the same bitline [317] in a small portion of a DRAM array. We refer the reader to ComputeDRAM [102] for a detailed description of how real chips can perform majority operations.

Methodology. We perform bitwise AND/OR operations by issuing DRAM command sequences to DRAM modules in quick succession by violating standard DRAM timing parameters. Listing 3 depicts the key code block that we use to generate DRAM Bender programs for our experiment.

```
1  p.appendACT(BANK, false, R1, false, N);
2  p.appendPRE(BANK, false, false, M);
3  p.appendACT(BANK, false, R2, false);
```

Listing 3: DRAM Bender code segment to perform a bitwise majority operation

We send the first `ACT` command to row address R1, and the second `ACT` command to row address *R2*. We select R1 and R2 such that they correspond to the second and the third row in a contiguous set of four DRAM rows (e.g., row addresses 0, 1, 2, 3), which we call a *DRAM segment*. For example, the first row in the second DRAM segment in a bank has the row address 4. Thus, R1 and R2 are 5 and 6 when we want to perform bitwise AND/OR in the second segment. In a segment, we initialize the *second row* with *all-ones* and place the operands in the first and the third rows to perform an OR operation, and initialize the *first row* with *all-zeros* and place the operands in the second and the third rows to perform an AND operation [102]. We test a total number of 8K segments in one DRAM bank and calculate the bit error rate (BER) of the bitwise AND/OR operations for

each segment. We sweep the values of $tRAS$ (N in Listing 3) and tRP (M in Listing 3) from 1.5 ns to 15 ns with increments of 1.5 ns, and test a total number of 100 different $tRAS$ and tRP combinations.

Results. We make the key observation from our experiments that we can perform valid majority AND/OR operations (i.e., we observe that multiple rows are activated with the execution of the ACT→ PRE→ ACT command sequence) on DRAM chips from one DRAM manufacturer (i.e., SK Hynix) when we use the following ($tRAS$, tRP) timing combinations: (1.5 ns, 1.5 ns), (1.5 ns, 3.0 ns), and (3.0 ns, 1.5 ns).

Figure 12 depicts the proportion of rows that can perform AND/OR operations with smaller BER than what is displayed on the x-axis. Each bar is composed of three stacks: *(i)* the blue stack represents the number of segments that can perform AND operations, but not OR operations, *(ii)* the green stack represents the number that can perform OR operations, but not AND operations, and *(iii)* the gold stack represents the number that can perform both AND/OR operations, all proportional to the number of segments that can correctly perform either one or both of the operations. There is heterogeneity in the BER in terms of the operation (AND/OR) being performed. We find that *(i)* AND operations produce more reliable results than OR operations. 35 segments support *only* AND operations at less than 3% BER and the smallest observed BER is 1.9% for AND operations. *(ii)* The number of segments that support AND/OR operations significantly increases as BER increases: 160 segments support AND/OR with $< 5\%$ BER, whereas 4546 segments support AND/OR with $< 10\%$ BER.

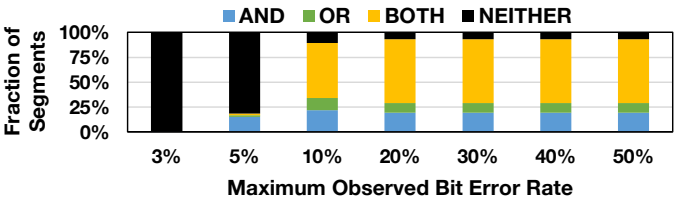


Figure 12: The fraction of DRAM segments that support AND, OR, both (AND and OR) of, and neither of the operations.

Conclusion. We conclude that new-generation DDR4 chips support in-DRAM bitwise AND/OR operations. Although we do not find any DRAM segments that support AND/OR operations with 0% BER, our results align with prior work on DDR3 chips [102]. We make a new observation that there is heterogeneity in BER in terms of the bitwise operation performed, which can be leveraged by approximate computing techniques to perform more accurate computation [202]. For example, a workload could place its bitwise AND operations' operands into segments with a smaller BER for AND operations.

4.4. Research Enabled by DRAM Bender

DRAM Bender has already enabled several prior works on read disturbance characterization [97, 133, 193, 233, 275, 277, 374], evaluation of existing RowHammer mitigations [97, 133], true random number generation [272], uncovering undocumented functionality in DRAM [375], and approximate DRAM for efficient deep neural network inference [202]. Parts of DRAM Bender's hardware design were reused in developing an end-to-end processing-in-DRAM framework [270] and an HBM2 DRAM testing infrastructure [271].

All of these works have provided significant contributions and advanced the state-of-the-art in their respective areas. Particularly, the works that evaluate RowHammer mitigation mechanisms used in real DDR4 DRAM chips demonstrated that these DRAM chips are *not* RowHammer-free, contrary to major DRAM manufacturers' claims [97, 133] and thus enabled significant changes in industry [262].

The artifacts of two of the prior works that use DRAM Bender, U-TRR [133] and QUAC-TRNG [272], are already freely and openly available [303, 304]. The open source artifacts of other prior work [97, 193, 202, 277, 374, 375] that used DRAM Bender are work-in-progress and we plan to release them as part of our future work.

We believe that these prior works demonstrate the versatility and ease of use of DRAM Bender in enabling impactful research. We hope that such versatility and ease of use accelerates the adoption of DRAM Bender by researchers in academia and industry to perform experiments on state-of-the-art DRAM chips.

5. New Research Directions

DRAM Bender users can conduct studies on state-of-the-art DRAM chips with no interface restrictions. We discuss two concrete example research directions.

5.1. Characterization of RowHammer

DRAM Bender enables open study of DRAM security and reliability issues using state-of-the-art chips. DRAM Bender openly and freely enables studies that evaluate and verify the security guarantees provided by RowHammer mitigation mechanisms implemented in real DDR4 devices (similar to [97, 133]). Since DDR4 DRAM is widely used in current and near-future computing systems, many systems can be vulnerable to attacks that can escalate user privileges, leak confidential data and perform denial of service if bit-flips are exploitable. It is important to rigorously understand the RowHammer problem [262] and other potential vulnerabilities that may lead to bit-flips (e.g., data retention errors) and openly evaluate any existing mitigations in order to develop effective and comprehensive solutions to RowHammer and other potential vulnerabilities. DRAM Bender can enable new studies similar to [97, 133] as well as other studies that might discover other issues in state-of-the-art DRAM chips.

5.2. Power Consumption Studies

Prior works [108, 349] show that the existing DRAM power models are not accurate for two key reasons. First, manufacturer-defined guardbands, provided in data sheets, prevent one from understanding the real power consumption characteristics of DRAM chips and can be misleading regarding the power consumption variation across different manufacturers, die revisions, and technology nodes. Second, standard power consumption values, referred to as $IDD(N)$ and $ICC(N)$ values, do not cover the worst-case (i.e., peak) power consumption of real chips due to static and limited data patterns used during these measurements, as specified in technical

documents [157, 159, 160, 160-163, 246, 248, 249]. Therefore, it is important for future research to understand a DRAM chip's power consumption under different conditions [58, 108].

Unfortunately, publicly available DRAM testing infrastructures are not capable of accurately measuring a DRAM's energy consumption. The state-of-the-art, SoftMC [134], has a limited capacity (8K) DRAM command queue with no control flow support for branch and jump operations, causing a given command sequence to be completed within less than $10\,\mu s$, after which a new command sequence must be transmitted from a host machine to the FPGA-based platform which can incur latency in the order of ms, depending on the host machine's state. Therefore, accurately measuring a DRAM chip's power consumption with SoftMC requires employing power measurement equipment with a MHz sampling rate. However, even high-end current measuring equipment [178] have sampling rates of fewer than $10\,kHz$ [108]. To overcome this limitation, Ghose et al. [108] report that they heavily modify SoftMC [134] to allow the command sequence to be executed in an infinite loop. Unfortunately, their modifications are not publicly available and it is not clear if their test setup can be used for standards newer than DDR3.

DRAM Bender's programmer interface allows a user to create loops to repeat executing a command sequence as many times as needed for power measurement equipment to accurately capture the power consumption. We believe that DRAM Bender will enable future studies on DRAM power consumption, which is a first-order concern on a wide spectrum of systems, including servers, mobile devices, and battery-backed edge devices.

6. Related Work

DRAM Bender enables experimental studies on state-of-the-art DRAM chips by providing an open, easy-to-use, and extensible DRAM testing infrastructure. We already extensively discuss the shortcomings of existing open source DRAM testing infrastructures in Section 2.6. We now compare DRAM Bender against other infrastructures and platforms.

Besides SoftMC [134] and LRT [17], there exist other infrastructures used for testing DRAM chips [1, 43, 100, 139, 142, 177, 235, 268, 340]. Unfortunately, those infrastructures suffer from at least one of the following three shortcomings: 1) support for limited and fixed test patterns [1, 100, 268, 340], 2) poor usability due to lack of flexibility and open source code [139, 142, 177], and 3) lack of programmability [43]. DRAM chips include a mechanism called Built-In Self-Test (BIST) (e.g., [4-6, 35, 81, 82, 123, 151, 243, 244, 292, 293, 333, 377, 382]) to conduct fixed test patterns. Unfortunately, BIST 1) provides only a limited number of fixed tests that are not programmable, 2) lacks flexibility and visibility to perform many experiments, and 3) is implemented only in a limited set of DRAM chips [134]. In contrast, as we demonstrate, DRAM Bender provides an extensible design and an easy-to-use API. DRAM Bender fully exposes the underlying DRAM interface to the user to allow precisely crafting a desired access pattern. DRAM Bender users can conduct tests using either a supported FPGA board and DRAM standard out of the box or a new FPGA board and a new DRAM standard with relatively simple modifications.

Prior works develop other open source FPGA-based frameworks for 1) evaluating processing-in-memory (PIM) techniques on real DRAM chips on real systems [270], 2) facilitating the emulation of PIM architectures and prototyping new PIM techniques [251], and 3) evaluating HBM-based processing-near-memory (PNM) architectures [386]. Although useful in conducting real system evaluation of PIM and PNM techniques using contemporary workloads (e.g., performance, energy), unlike DRAM Bender, these frameworks cannot be used to study the performance, reliability, and security characteristics of real, state-of-the-art DRAM chips.

7. Future Work and Limitations

Support For New DRAM Interfaces. We leave the integration of new DRAM interfaces, such as DDR5 [163], to improve the versatility of DRAM Bender to future work. DDR5 implements new commands to improve the performance and reliability of DRAM. In particular, the `RFM` command triggers a refresh management operation within the DRAM device, performing target row refresh (TRR) operations to alleviate RowHammer-induced bit-flips. Like other TRR mechanisms implemented in the current generation of DDRX interfaces, it is unclear if `RFM` can solve the RowHammer problem [97]. We hope to enable studies on `RFM` going forward as we integrate support for the DDR5 interface.

Support for New FPGA Boards. DRAM Bender is already prototyped on two different Xilinx boards and three different Bittware FPGA boards (Section 3.4). Increasing the number of FPGA board prototypes is critical for DRAM Bender to be more widely adopted as a DRAM testing infrastructure. More DRAM Bender prototypes would allow a greater set of researchers with a limited number of FPGA boards in their inventories to use DRAM Bender out of the box.

Power Measurement Setup. A DDRx power measurement setup for DRAM Bender is work-in-progress. We aim to release a manual describing how to build a power measurement setup as part of future work in our Github repository [302]. The planned power measurement setup is based on a prior work [108] and consists of three major components. First, a *DIMM riser board* (e.g., JET-5612 [245]) is placed between the DDRx socket on the FPGA board and the DDRx module under test. The riser board exposes the DDRx DIMM's voltage rails for current probing via shunt resistors. Second, a *high-precision current sensor* (e.g., Keysight 34134A [178]) connects to the shunt resistors and measures the current on the DDRx voltage rails. Third, a *high-precision multimeter* (e.g., Keysight 34461A [179]) is coupled with the current sensor to report current measurements.

Packetized Interfaces. A subset of the current 3D stacked DRAM devices (e.g., HMC [247]) implement *packetized* interfaces that use high-speed serial links to communicate with the host processing unit. In such devices, the controller that communicates with the DRAM dies resides in the logic layer of the device. Therefore, memory packets specify operations at a

higher level (e.g., `load` and `store`) compared to synchronous interfaces (e.g., `ACT`, `PRE`, `READ`). In an FPGA-based platform that supports such an interface, this would prevent DRAM Bender from fully exposing the DRAM interface to the user as it would need to communicate with the DRAM device using higher-level operations. Hence, the packetized interface is a limiting factor in integrating support for a subset of current 3D stacked DRAM devices (e.g., HMC) in DRAM Bender.

Graphical User Interface. A graphical user interface (GUI) could provide DRAM Bender with a more intuitive and user-friendly interface for conducting experiments. We already open sourced DRAM Bender on Github [302]. We believe that the open source repository will allow for a collaborative effort from many other researchers and users of the infrastructure to develop new valuable features, such as a GUI.

8. Conclusion

We develop a new open source DRAM testing infrastructure that is versatile, extensible, and easy to use. Unlike existing open source infrastructures, DRAM Bender provides both *(i)* a nonrestrictive interface to DRAM devices and *(ii)* an extensible design. Its nonrestrictive API allows users to issue DRAM commands in an arbitrary order and at arbitrary times. It comprises a modular design that enables easily integrating new DRAM interfaces and porting to different FPGA boards. We demonstrate DRAM Bender's *(i)* versatility and ease of use by conducting three new studies that show how DRAM Bender successfully enables new insights into the characteristics of modern DDR4 DRAM chips, and *(ii)* extensibility by porting it to five FPGA boards with either DDR3 or DDR4 support. We hope that with its versatility, ease of use, and extensible design, DRAM Bender will be the mainstream infrastructure used in experimental DRAM studies and will be useful in developing new mechanisms and methodologies that improve DRAM security, reliability, performance, and efficiency.

Acknowledgements

We thank the anonymous reviewers of TCAD, ISCA 2022, and HPCA 2022 for feedback. We thank the SAFARI Research Group members for valuable feedback and the stimulating intellectual environment they provide. We acknowledge the generous gift funding provided by our industrial partners (especially Google, Huawei, Intel, Microsoft, VMware). This work was in part supported by a Google Security and Privacy Research Award and the Microsoft Swiss Joint Research Center.

References

[1] Advantest, "V6000 Memory Platform," https://www.advantest.com/products/ic-test-systems/v6000-memory.
[2] M. T. Aga *et al.*, "When Good Protections Go Bad: Exploiting Anti-DoS Measures to Accelerate Rowhammer Attacks," in *HOST*, 2017.
[3] S. Aga *et al.*, "Compute Caches," in *HPCA*, 2017.
[4] V. Agrawal *et al.*, "A Tutorial on Built-In Self-Test. I. Principles," *IEEE Design & Test of Computers*, 1993.
[5] V. Agrawal *et al.*, "A Tutorial on Built-In Self-Test. II. Applications," *IEEE Design & Test of Computers*, 1993.
[6] V. D. Agrawal *et al.*, "Built-In Self-Test for Digital Integrated Circuits," *AT&T Technical Journal*, 1994.
[7] H. Ahmed *et al.*, "A Compiler for Automatic Selection of Suitable Processing-in-Memory Instructions," in *DATE*, 2019.
[8] J. Ahn *et al.*, "A Scalable Processing-in-Memory Accelerator for Parallel Graph Processing," in *ISCA*, 2015.
[9] J. Ahn *et al.*, "PIM-Enabled Instructions: A Low-Overhead, Locality-Aware Processing-in-Memory Architecture," in *ISCA*, 2015.
[10] S. M. Ajorpaz *et al.*, "EVAX: Towards a Practical, Pro-active & Adaptive Architecture for High Performance & Security," in *MICRO*, 2022.
[11] B. Akin *et al.*, "Data Reorganization in Memory Using 3D-Stacked DRAM," in *ISCA*, 2015.
[12] M. F. Ali *et al.*, "In-Memory Low-Cost Bit-Serial Addition Using Commodity DRAM Technology," in *TCAS-I*, 2019.
[13] S. Angizi *et al.*, "PIMA-Logic: A Novel Processing-in-Memory Architecture for Highly Flexible and Energy-efficient Logic Computation," in *DAC*, 2018.
[14] S. Angizi *et al.*, "CMP-PIM: An Energy-efficient Comparator-based Processing-in-Memory Neural Network Accelerator," in *DAC*, 2018.
[15] S. Angizi *et al.*, "AlignS: A Processing-in-Memory Accelerator for DNA Short Read Alignment Leveraging SOT-MRAM," in *DAC*, 2019.
[16] S. Angizi *et al.*, "Graphide: A Graph Processing Accelerator Leveraging In-DRAM-computing," in *GLSVLSI*, 2019.
[17] Antmicro, "LiteX Row Hammer Tester — GitHub Repository," https://github.com/antmicro/litex-rowhammer-tester.
[18] Antmicro, "Why is EtherBone bridge so slow?" https://github.com/antmicro/litex-rowhammer-tester/issues/4.
[19] Apple Inc., "About the Security Content of Mac EFI Security Update 2015-001," https://support.apple.com/en-us/HT204934, 2015.
[20] K. Arıkan *et al.*, "Processor Security: Detecting Microarchitectural Attacks via Count-min Sketches," *VLSI*, 2022.
[21] ARM, *AMBA AXI and ACE Protocol Specification AXI3, AXI4, and AXI4-Lite ACE and ACE-Lite*, 2013.
[22] B. Asgari *et al.*, "FAFNIR: Accelerating Sparse Gathering by Using Efficient Near-Memory Intelligent Reduction," in *HPCA*, 2021.
[23] H. Asghari-Moghaddam *et al.*, "Chameleon: Versatile and Practical Near-DRAM Acceleration Architecture for Large Memory Systems," in *MICRO*, 2016.
[24] Z. B. Aweke *et al.*, "ANVIL: Software-Based Protection Against Next-Generation Rowhammer Attacks," in *ASPLOS*, 2016.
[25] H. Aydin *et al.*, "Cyber Security in Industrial Control Systems (ICS): A Survey of RowHammer Vulnerability," *Applied Computer Science*, 2022.
[26] O. O. Babarinsa *et al.*, "JAFAR: Near-Data Processing for Databases," in *SIGMOD*, 2015.
[27] B. M. S. Bahar Talukder *et al.*, "Exploiting DRAM Latency Variations for Generating True Random Numbers," in *ICCE*, 2019.
[28] K. Bains *et al.*, "Row Hammer Refresh Command," US Patents: 9,117,544 9,236,110 10,210,925, 2015.
[29] K. Bains *et al.*, "Method, Apparatus and System for Providing a Memory Refresh," US Patent: 9,030,903, 2015.
[30] K. S. Bains *et al.*, "Distributed Row Hammer Tracking," US Patent: 9,299,400, 2016.
[31] K. S. Bains *et al.*, "Row Hammer Monitoring Based on Stored Row Hammer Threshold Value," US Patent: 10,083,737, 2016.
[32] R. Balasubramonian *et al.*, "Near-Data Processing: Insights from a MICRO-46 Workshop," *IEEE Micro*, 2014.
[33] A. Barenghi *et al.*, "Software-only Reverse Engineering of Physical DRAM Mappings for Rowhammer Attacks," in *IVSW*, 2018.
[34] T. Bennett *et al.*, "Panopticon: A Complete In-DRAM Rowhammer Mitigation," in *DRAMSec*, 2021.
[35] P. Bernardi *et al.*, "A Programmable BIST for DRAM Testing and Diagnosis," in *ITC*, 2010.
[36] M. Besta *et al.*, "SISA: Set-Centric Instruction Set Architecture for Graph Mining on Processing-in-Memory Systems," in *MICRO*, 2021.
[37] D. Bhattacharjee *et al.*, "ReVAMP: ReRAM based VLIW Architecture for In-memory Computing," in *DATE*, 2017.
[38] S. Bhattacharya *et al.*, "Curious Case of RowHammer: Flipping Secret Exponent Bits using Timing Analysis," in *CHES*, 2016.
[39] S. Bhattacharya *et al.*, "Advanced Fault Attacks in Software: Exploiting the Rowhammer Bug," in *Fault Tolerant Architectures for Cryptography and Hardware Security*, 2018.
[40] BittWare, "Bittware XUPP3R FPGA Board," https://www.bittware.com/fpga/xup-p3r/.
[41] BittWare, "Bittware XUPVVH FPGA Board," https://www.bittware.com/fpga/xup-vvh/.
[42] BittWare, "Bittware XUSP3S FPGA Board," https://www.bittware.com/fpga/xus-p3s/.
[43] M. N. Bojnordi *et al.*, "PARDIS: A Programmable Memory Controller for the DDRx Interfacing Standards," in *ISCA*, 2012.
[44] A. Boroumand *et al.*, "Google Workloads for Consumer Devices: Mitigating Data Movement Bottlenecks," in *ASPLOS*, 2018.
[45] A. Boroumand, "Practical Mechanisms for Reducing Processor-Memory Data Movement in Modern Workloads," Ph.D. dissertation, Carnegie Mellon University, 2020.
[46] A. Boroumand *et al.*, "Google Neural Network Models for Edge Devices: Analyzing and Mitigating Machine Learning Inference Bottlenecks," arXiv:2109.14320, 2021.
[47] A. Boroumand *et al.*, "Google Neural Network Models for Edge Devices: Analyzing and Mitigating Machine Learning Inference Bottlenecks," in *PACT*, 2021.
[48] A. Boroumand *et al.*, "Polynesia: Enabling Effective Hybrid Transactional/Analytical Databases with Specialized Hardware/Software Co-Design," arXiv:2103.00798, 2021.
[49] A. Boroumand *et al.*, "Polynesia: Enabling Effective Hybrid Transactional Analytical Databases with Specialized Hardware Software Co-Design," in *ICDE*, 2022.
[50] A. Boroumand *et al.*, "LazyPIM: An Efficient Cache Coherence Mechanism for Processing-in-Memory," *CAL*, 2016.
[51] A. Boroumand *et al.*, "CoNDA: Enabling Efficient Near-Data Accelerator Communication by Optimizing Data Movement," *ISCA*, 2019.
[52] E. Bosman *et al.*, "Dedup Est Machina: Memory Deduplication as An Advanced Exploitation Vector," in *S&P*, 2016.
[53] F. Brasser *et al.*, "Can't Touch This: Software-Only Mitigation Against Rowhammer Attacks Targeting Kernel Memory," in *USENIX Security*, 2017.
[54] W. Burleson *et al.*, "Invited: Who is the Major Threat to Tomorrow's Security? You, the Hardware Designer," in *DAC*, 2016.

[55] K. Cai *et al.*, "On the Feasibility of Training-time Trojan Attacks through Hardware-based Faults in Memory," in *HOST*, 2022.
[56] D. S. Cali *et al.*, "GenASM: A High-Performance, Low-Power Approximate String Matching Acceleration Framework for Genome Sequence Analysis," in *MICRO*, 2020.
[57] S. Carre *et al.*, "OpenSSL Bellcore's Protection Helps Fault Attack," in *DSD*, 2018.
[58] K. Chandrasekar *et al.*, "DRAMPower: Open-Source DRAM Power & Energy Estimation Tool," http://www.drampower.info/.
[59] K. K. Chang, "Understanding and Improving the Latency of DRAM-Based Memory Systems," Ph.D. dissertation, Carnegie Mellon Univ., 2017.
[60] K. K. Chang *et al.*, "Understanding Latency Variation in Modern DRAM Chips: Experimental Characterization, Analysis, and Optimization," in *SIGMETRICS*, 2016.
[61] K. K. Chang *et al.*, "Improving DRAM Performance by Parallelizing Refreshes with Accesses," in *HPCA*, 2014.
[62] K. K. Chang *et al.*, "Low-Cost Inter-Linked Subarrays (LISA): Enabling Fast Inter-Subarray Data Movement in DRAM," in *HPCA*, 2016.
[63] K. K. Chang *et al.*, "Understanding Reduced-Voltage Operation in Modern DRAM Devices: Experimental Characterization, Analysis, and Mechanisms," in *SIGMETRICS*, 2017.
[64] P. Chi *et al.*, "Prime: A Novel Processing-in-memory Architecture for Neural Network Computation in Reram-based Main Memory," in *ISCA*, 2016.
[65] S. Cho *et al.*, "McDRAM v2: In-Dynamic Random Access Memory Systolic Array Accelerator to Address the Large Model Problem in Deep Neural Networks on the Edge," *IEEE Access*, 2020.
[66] J. Choi *et al.*, "Multiple Clone Row DRAM: A Low Latency and Area Optimized DRAM," in *ISCA*, 2015.
[67] Y. Cohen *et al.*, "HammerScope: Observing DRAM Power Consumption Using Rowhammer," in *CCS*, 2022.
[68] L. Cojocar *et al.*, "Are We Susceptible to Rowhammer? An End-to-End Methodology for Cloud Providers," in *S&P*, 2020.
[69] L. Cojocar *et al.*, "Exploiting Correcting Codes: On the Effectiveness of ECC Memory Against Rowhammer Attacks," in *S&P*, 2019.
[70] G. Dai *et al.*, "GraphH: A Processing-in-Memory Architecture for Large-scale Graph Processing," *IEEE TCAD*, 2018.
[71] F. de Ridder *et al.*, "SMASH: Synchronized Many-Sided Rowhammer Attacks from JavaScript," in *USENIX Security*, 2021.
[72] Q. Deng *et al.*, "DrAcc: A DRAM Based Accelerator for Accurate CNN Inference," in *DAC*, 2018.
[73] R. H. Dennard, "Field-Effect Transistor Memory," 1968, U.S. Patent 3,387,286.
[74] A. Denzler *et al.*, "Casper: Accelerating Stencil Computation using Near-cache Processing," *IEEE Access*, 2023.
[75] F. Devaux *et al.*, "Method and Circuit for Protecting a DRAM Memory Device from the Row Hammer Effect," US Patent: 10,885,966, 2021.
[76] DFI Group, *DFI 5.0 Specification*, July 2018.
[77] A. Di Dio *et al.*, "Copy-on-Flip: Hardening ECC Memory Against Rowhammer Attacks," in *NDSS*, 2023.
[78] S. Diab *et al.*, "High-throughput Pairwise Alignment with the Wavefront Algorithm using Processing-in-Memory," arXiv:2204.02085, 2022.
[79] S. Diab *et al.*, "High-throughput Pairwise Alignment with the Wavefront Algorithm using Processing-in-Memory," in *HICOMB*, 2022.
[80] J. Draper *et al.*, "The Architecture of the DIVA Processing-in-Memory Chip," in *SC*, 2002.
[81] J. Dreibelbis *et al.*, "Processor-Based Built-In Self-Test for Embedded DRAM," *IEEE Journal of Solid-State Circuits*, 1998.
[82] J. Dreibelbis *et al.*, "An ASIC Library Granular DRAM Macro with Built-In Self-Test," in *ISSCC*, 1998.
[83] M. Drumond *et al.*, "The Mondrian Data Engine," in *ISCA*, 2017.
[84] C. Eckert *et al.*, "Neural Cache: Bit-serial In-cache Acceleration of Deep Neural Networks," in *ISCA*, 2018.
[85] D. G. Elliott *et al.*, "Computational RAM: Implementing Processors in Memory," *IEEE Design & Test of Computers*, 1999.
[86] S. Enomoto *et al.*, "Efficient Protection Mechanism for CPU Cache Flush Instruction Based Attacks," *IEICE Transactions on Information and Systems*, 2022.
[87] M. J. Fahr, "The Effects of Side-Channel Attacks on Post-Quantum Cryptography: Influencing FrodoKEM Key Generation Using the Rowhammer Exploit," Master's thesis, University of Arkansas, 2022.
[88] M. Fahr Jr *et al.*, "When Frodo Flips: End-to-End Key Recovery on FrodoKEM via Rowhammer," *CCS*, 2022.
[89] A. Fakhrzadehgan *et al.*, "SafeGuard: Reducing the Security Risk from Row-Hammer via Low-Cost Integrity Protection," in *HPCA*, 2022.
[90] A. Farmahini-Farahani *et al.*, "NDA: Near-DRAM Acceleration Architecture Leveraging Commodity DRAM Devices and Standard Memory Modules," in *HPCA*, 2015.
[91] I. Fernandez *et al.*, "NATSA: A Near-Data Processing Accelerator for Time Series Analysis," in *ICCD*, 2020.
[92] J. D. Ferreira *et al.*, "pLUTo: In-DRAM Lookup Tables to Enable Massively Parallel General-Purpose Computation," in *MICRO*, 2022.
[93] A. P. Fournaris *et al.*, "Exploiting Hardware Vulnerabilities to Attack Embedded System Devices: A Survey of Potent Microarchitectural Attacks," *Electronics*, 2017.
[94] L. France *et al.*, "Modeling Rowhammer in the gem5 Simulator," in *CHES 2022-Conference on Cryptographic Hardware and Embedded Systems*, 2022.
[95] L. France *et al.*, "Reducing the Silicon Area Overhead of Counter-Based Rowhammer Mitigations," in *18th CryptArchi Workshop*, 2022.
[96] P. Frigo *et al.*, "Grand Pwning Unit: Accelerating Microarchitectural Attacks with the GPU," in *S&P*, 2018.
[97] P. Frigo *et al.*, "TRRespass: Exploiting the Many Sides of Target Row Refresh," in *S&P*, 2020.
[98] D. Fujiki *et al.*, "In-Memory Data Parallel Processor," in *ASPLOS*, 2018.
[99] D. Fujiki *et al.*, "Duality Cache for Data Parallel Acceleration," in *ISCA*, 2019.
[100] FuturePlus, "FS2800 DDR Detective," http://www.futureplus.com/DDR-Detective-Standalone/summary-2800.html.
[101] P.-E. Gaillardon *et al.*, "The Programmable Logic-in-Memory (PLiM) Computer," in *DATE*, 2016.
[102] F. Gao *et al.*, "ComputeDRAM: In-Memory Compute Using Off-the-Shelf DRAMs," in *MICRO*, 2019.
[103] M. Gao *et al.*, "Practical Near-Data Processing for In-Memory Analytics Frameworks," in *PACT*, 2015.
[104] M. Gao *et al.*, "HRL: Efficient and Flexible Reconfigurable Logic for Near-Data Processing," in *HPCA*, 2016.
[105] M. Gao *et al.*, "Tetris: Scalable and Efficient Neural Network Acceleration with 3D Memory," in *ASPLOS*, 2017.
[106] S. Gautam *et al.*, "Row Hammering Mitigation Using Metal Nanowire in Saddle Fin DRAM," *IEEE TED*, 2019.
[107] S. Ghose *et al.*, "Processing-in-Memory: A Workload-Driven Perspective," *IBM JRD*, 2019.
[108] S. Ghose *et al.*, "What Your DRAM Power Models Are Not Telling You: Lessons from a Detailed Experimental Study," in *SIGMETRICS*, 2018.
[109] C. Giannoula *et al.*, "SparseP: Towards Efficient Sparse Matrix Vector Multiplication on Real Processing-In-Memory Systems," arXiv:2201.05072, 2022.
[110] C. Giannoula *et al.*, "Towards Efficient Sparse Matrix Vector Multiplication on Real Processing-in-Memory Architectures," in *SIGMETRICS*, 2022.
[111] C. Giannoula *et al.*, "SynCron: Efficient Synchronization Support for Near-Data-Processing Architectures," in *HPCA*, 2021.
[112] M. Gokhale *et al.*, "Processing in Memory: The Terasys Massively Parallel PIM Array," *IEEE Computer*, 1995.
[113] M. Gokhale *et al.*, "Near Memory Data Structure Rearrangement," in *MEMSYS*, 2015.
[114] Z. Greenfield *et al.*, "Throttling Support for Row-Hammer Counters," 2016, U.S. Patent 9,251,885.
[115] D. Gruss *et al.*, "Another Flip in the Wall of Rowhammer Defenses," in *S&P*, 2018.
[116] D. Gruss *et al.*, "Rowhammer.js: A Remote Software-Induced Fault Attack in Javascript," in *DIMVA*, 2016.
[117] B. Gu *et al.*, "Biscuit: A Framework for Near-Data Processing of Big Data Workloads," in *ISCA*, 2016.
[118] P. Gu *et al.*, "iPIM: Programmable In-Memory Image Processing Accelerator using Near-Bank Architecture," in *ISCA*, 2020.
[119] C. Gude Ramarao *et al.*, "Defending SoCs with FPGAs from Rowhammer Attacks," *Material Science*, 2023.
[120] K. Guha *et al.*, "Criticality based Reliability from Rowhammer Attacks in Multi-User-Multi-FPGA Platform," in *VLSID*. IEEE, 2022.
[121] Q. Guo *et al.*, "3D-Stacked Memory-Side Acceleration: Accelerator and System Design," in *WoNDP*, 2014.
[122] N. Hajinazar *et al.*, "SIMDRAM: A Framework for Bit-Serial SIMD Processing Using DRAM," in *ASPLOS*, 2021.
[123] A.-W. Hakmi *et al.*, "Programmable deterministic Built-In Self-Test," in *IEEE International Test Conference*, 2007.
[124] T. Hamamoto *et al.*, "On the Retention Time Distribution of Dynamic Random Access Memory (DRAM)," *Electron Devices*, 1998.
[125] S. Hamdioui *et al.*, "Memristor for Computing: Myth or Reality?" in *DATE*, 2017.
[126] S. Hamdioui *et al.*, "Memristor Based Computation-in-Memory Architecture for Data-intensive Applications," in *DATE*, 2015.
[127] J.-W. Han *et al.*, "Surround Gate Transistor With Epitaxially Grown Si Pillar and Simulation Study on Soft Error and Rowhammer Tolerance for DRAM," *IEEE TED*, 2021.
[128] M. Hashemi *et al.*, "Continuous Runahead: Transparent Hardware Acceleration for Memory Intensive Workloads," in *MICRO*, 2016.
[129] M. Hashemi *et al.*, "Accelerating Dependent Cache Misses with an Enhanced Memory Controller," in *ISCA*, 2016.
[130] H. Hassan *et al.*, "CROW: A Low-Cost Substrate for Improving DRAM Performance, Energy Efficiency, and Reliability," in *ISCA*, 2019.
[131] H. Hassan *et al.*, "A Case for Self-Managing DRAM Chips: Improving Performance, Efficiency, Reliability, and Security via Autonomous in-DRAM Maintenance Operations," arXiv:2207.13358, 2022.
[132] H. Hassan *et al.*, "ChargeCache: Reducing DRAM Latency by Exploiting Row Access Locality," in *HPCA*, 2016.
[133] H. Hassan *et al.*, "Uncovering In-DRAM RowHammer Protection Mechanisms: A New Methodology, Custom RowHammer Patterns, and Implications," in *MICRO*, 2021.
[134] H. Hassan *et al.*, "SoftMC: A Flexible and Practical Open-Source Infrastructure for Enabling Experimental DRAM Studies," in *HPCA*, 2017.
[135] J. M. Herruzo *et al.*, "Enabling Fast and Energy-Efficient FM-Index Exact Matching Using Processing-Near-Memory," *The Journal of Supercomputing*, 2021.
[136] Hewlett-Packard Enterprise, "HP Moonshot Component Pack Version 2015.05.0," http://h17007.www1.hp.com/us/en/enterprise/servers/products/moonshot/component-pack/index.aspx, 2015.
[137] S. Hong *et al.*, "Terminal Brain Damage: Exposing the Graceless Degradation in Deep Neural Networks Under Hardware Fault Attacks," in *USENIX Security*, 2019.
[138] S. Hong *et al.*, "DSAC: Low-Cost Rowhammer Mitigation Using In-DRAM Stochastic and Approximate Counting Algorithm," arXiv:2302.03591, 2023.
[139] C. Hou *et al.*, "An FPGA-Based Test Platform for Analyzing Data Retention Time Distribution of DRAMs," in *VLSI-DAT*, 2013.
[140] K. Hsieh *et al.*, "Accelerating Pointer Chasing in 3D-Stacked Memory: Challenges, Mechanisms, Evaluation," in *ICCD*, 2016.
[141] K. Hsieh *et al.*, "Transparent Offloading and Mapping (TOM): Enabling Programmer-Transparent Near-Data Processing in GPU Systems," in *ISCA*, 2016.
[142] J. Huang *et al.*, "An FPGA-Based Re-Configurable Functional Tester for Memory Chips," in *ATS*, 2000.
[143] Y. Huang *et al.*, "A Heterogeneous PIM Hardware-Software Co-Design for Energy-Efficient Graph Processing," in *IPDPS*, 2020.
[144] W.-M. Hwu *et al.*, "Rebooting the Data Access Hierarchy of Computing Systems," in *ICRC*, 2017.
[145] Intel, *Functional Description—RLDRAM 3 PHY-Only IP*, 2014.
[146] Intel, *External Memory Interface Handbook Volume 3: Reference Material*, 2019.

[147] Intel, *Multi Channel DMA Intel FPGA IP for PCI Express User Guide*, April 2022.
[148] E. Ipek *et al.*, "Self-Optimizing Memory Controllers: A Reinforcement Learning Approach," in *ISCA*, 2008.
[149] G. Irazoqui *et al.*, "MASCAT: Stopping Microarchitectural Attacks Before Execution," *IACR Cryptology*, 2016.
[150] S. Islam *et al.*, "Signature Correction Attack on Dilithium Signature Scheme," in *Euro S&P*, 2022.
[151] K. Itoh, *VLSI Memory Chip Design*. Springer, 2001.
[152] A. C. Jacob *et al.*, "Compiling for the Active Memory Cube," Tech. rep. RC25644 (WAT1612-008). IBM Research Division, Tech. Rep., 2016.
[153] M. Jacobsen *et al.*, "RIFFA 2.1: A Reusable Integration Framework for FPGA Accelerators," *TRETS*, 2015.
[154] S. Jain *et al.*, "Computing-in-Memory with Spintronics," in *DATE*, 2018.
[155] Y. Jang *et al.*, "SGX-Bomb: Locking Down the Processor via Rowhammer Attack," in *SysTEX*, 2017.
[156] P. Jattke *et al.*, "Blacksmith: Scalable Rowhammering in the Frequency Domain," in *S&P*, 2022.
[157] JEDEC, "Low Power Double Data Rate 2 (LPDDR2)," 2011.
[158] JEDEC, *JESD79-3: DDR3 SDRAM Standard*, 2012.
[159] JEDEC, "Low Power Double Data Rate 3 (LPDDR3)," Standard No. JESD209-3B, 2013.
[160] JEDEC, *JESD209-4B: Low Power Double Data Rate 4 (LPDDR4) Standard*, 2017.
[161] JEDEC, *JESD209-5A: LPDDR5 SDRAM Standard*, 2020.
[162] JEDEC, *JESD79-4C: DDR4 SDRAM Standard*, 2020.
[163] JEDEC, *JESD79-5: DDR5 SDRAM Standard*, 2020.
[164] JEDEC, *JESD235D: High Bandwidth Memory DRAM (HBM1, HBM2)*, 2021.
[165] S. Ji *et al.*, "Pinpoint Rowhammer: Suppressing Unwanted Bit Flips on Rowhammer Attacks," in *ASIACCS*, 2019.
[166] B. K. Joardar *et al.*, "Learning to Mitigate RowHammer Attacks," in *DATE*, 2022.
[167] B. K. Joardar *et al.*, "Machine Learning-based Rowhammer Mitigation," *TCAD*, 2022.
[168] JU-JET Electronics, "JET-5608AA SODIMM Adapter," https://www.eztest.com.tw/service_2_detail/46.htm.
[169] J. Juffinger *et al.*, "CSI: Rowhammer–Cryptographic Security and Integrity Against Rowhammer," in *S&P*, 2023.
[170] I. Kang *et al.*, "CAT-TWO: Counter-Based Adaptive Tree, Time Window Optimized for DRAM Row-Hammer Prevention," *IEEE Access*, 2020.
[171] M. Kang *et al.*, "An Energy-Efficient VLSI Architecture for Pattern Recognition via Deep Embedding of Computation in SRAM," in *ICASSP*, 2014.
[172] U. Kang *et al.*, "Co-Architecting Controllers and DRAM to Enhance DRAM Process Scaling," in *The Memory Forum*, 2014.
[173] Y. Kang *et al.*, "FlexRAM: Toward an Advanced Intelligent Memory System," in *ICCD*, 1999.
[174] A. Kaur *et al.*, "Work-in-Progress: DRAM-MaUT: DRAM Address Mapping Unveiling Tool for ARM Devices," in *CASES*, 2022.
[175] W. H. Kautz, "Cellular Logic-in-Memory Arrays," *IEEE TC*, 1969.
[176] B. Keeth *et al.*, *DRAM Circuit Design: A Tutorial*. Wiley, 2001.
[177] D. Keezer *et al.*, "An FPGA-Based ATE Extension Module for Low-Cost Multi-GHz Memory Test," in *ETS*, 2015.
[178] Keysight, "34134A AC/DC DMM Current Probe User Manual," https://www.keysight.com/us/en/assets/9018-02464/user-manuals/9018-02464.pdf.
[179] Keysight, "Keysight Truevolt Series DMM Operating and Service Guide," https://www.keysight.com/us/en/assets/9018-03876/service-manuals/9018-03876.pdf.
[180] S. Khan *et al.*, "The Efficacy of Error Mitigation Techniques for DRAM Retention Failures: A Comparative Experimental Study," in *SIGMETRICS*, 2014.
[181] S. Khan *et al.*, "PARBOR: An Efficient System-Level Technique to Detect Data-Dependent Failures in DRAM," in *DSN*, 2016.
[182] S. Khan *et al.*, "A Case for Memory Content-Based Detection and Mitigation of Data-Dependent Failures in DRAM," *IEEE CAL*, 2016.
[183] S. Khan *et al.*, "Detecting and Mitigating Data-Dependent DRAM Failures by Exploiting Current Memory Content," in *MICRO*, 2017.
[184] D.-H. Kim *et al.*, "Architectural Support for Mitigating Row Hammering in DRAM Memories," *IEEE CAL*, 2014.
[185] D. Kim *et al.*, "Neurocube: A Programmable Digital Neuromorphic Architecture with High-Density 3D Memory," in *ISCA*, 2016.
[186] G. Kim *et al.*, "Toward Standardized Near-Data Processing with Unrestricted Data Placement for GPUs," in *SC*, 2017.
[187] J. Kim *et al.*, "The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency–Reliability Tradeoff in Modern DRAM Devices," in *HPCA*, 2018.
[188] J. Kim *et al.*, "D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput," in *HPCA*, 2019.
[189] J. S. Kim *et al.*, "GRIM-Filter: Fast Seed Location Filtering in DNA Read Mapping Using Processing-in-Memory Technologies," *BMC Genomics*, 2018.
[190] J. S. Kim *et al.*, "Solar-DRAM: Reducing DRAM Access Latency by Exploiting the Variation in Local Bitlines," in *ICCD*, 2018.
[191] J. S. Kim *et al.*, "The DRAM Latency PUF: Quickly Evaluating Physical Unclonable Functions by Exploiting the Latency-Reliability Tradeoff in Modern Commodity DRAM Devices," in *HPCA*, 2018.
[192] J. S. Kim *et al.*, "D-RaNGe: Using Commodity DRAM Devices to Generate True Random Numbers with Low Latency and High Throughput," in *HPCA*, 2019.
[193] J. S. Kim *et al.*, "Revisiting RowHammer: An Experimental Analysis of Modern Devices and Mitigation Techniques," in *ISCA*, 2020.
[194] M. J. Kim *et al.*, "Mithril: Cooperative Row Hammer Protection on Commodity DRAM Leveraging Managed Refresh," in *HPCA*, 2022.
[195] W. Kim *et al.*, "A 1.1 V 16Gb DDR5 DRAM with Probabilistic-Aggressor Tracking, Refresh-Management Functionality, Per-Row Hammer Tracking, a Multi-Step Precharge, and Core-Bias Modulation for Security and Reliability Enhancement," in *ISSCC*. IEEE, 2023.
[196] Y. Kim *et al.*, "Flipping Bits in Memory Without Accessing Them: An Experimental Study of DRAM Disturbance Errors," in *ISCA*, 2014.
[197] Y. Kim *et al.*, "ATLAS: A Scalable and High-Performance Scheduling Algorithm for Multiple Memory Controllers," in *HPCA*, 2010.
[198] Y. Kim *et al.*, "A Case for Exploiting Subarray-Level Parallelism (SALP) in DRAM," in *ISCA*, 2012.
[199] P. M. Kogge, "EXECUBE - A New Architecture for Scaleable MPPs," in *ICPP*, 1994.
[200] A. Kogler *et al.*, "Half-Double: Hammering From the Next Row Over," in *USENIX Security*, 2022.
[201] R. K. Konoth *et al.*, "ZebRAM: Comprehensive and Compatible Software Protection Against Rowhammer Attacks," in *OSDI*, 2018.
[202] S. Koppula *et al.*, "EDEN: Enabling Energy-Efficient, High-Performance Deep Neural Network Inference Using Approximate DRAM," in *MICRO*, 2019.
[203] S. Kvatinsky *et al.*, "MAGIC—Memristor-Aided Logic," *IEEE TCAS II: Express Briefs*, 2014.
[204] S. Kvatinsky *et al.*, "Memristor-Based IMPLY Logic Design Procedure," in *ICCD*, 2011.
[205] S. Kvatinsky *et al.*, "Memristor-Based Material Implication (IMPLY) Logic: Design Principles and Methodologies," *TVLSI*, 2014.
[206] A. Kwong *et al.*, "RAMBleed: Reading Bits in Memory Without Accessing Them," in *S&P*, 2020.
[207] J. Landgraf *et al.*, "Combining Emulation and Simulation to Evaluate a Near Memory Key/Value Lookup Accelerator," 2021.
[208] D. Lavenier *et al.*, "Variant Calling Parallelization on Processor-in-Memory Architecture," in *BIBM*, 2020.
[209] D. Lee *et al.*, "Design-induced Latency Variation in Modern DRAM Chips: Characterization, Analysis, and Latency Reduction Mechanisms," *POMACS*, 2017.
[210] D. Lee *et al.*, "Adaptive-Latency DRAM: Optimizing DRAM Timing for the Common-Case," in *HPCA*, 2015.
[211] D. Lee *et al.*, "Tiered-Latency DRAM: A Low Latency and Low Cost DRAM Architecture," in *HPCA*, 2013.
[212] D. Lee *et al.*, "Decoupled Direct Memory Access: Isolating CPU and IO Traffic by Leveraging a Dual-Data-Port DRAM," in *PACT*, 2015.
[213] E. Lee *et al.*, "TWiCe: Time Window Counter Based Row Refresh to Prevent Row-Hammering," *IEEE CAL*, 2018.
[214] G.-H. Lee *et al.*, "CryoGuard: A Near Refresh-Free Robust DRAM Design for Cryogenic Computing," in *ISCA*, 2021.
[215] J. H. Lee *et al.*, "BSSync: Processing Near Memory for Machine Learning Workloads with Bounded Staleness Consistency Models," in *PACT*, 2015.
[216] S. Lefforge, "Reverse Engineering Post-Quantum Cryptography Schemes to Find Rowhammer Exploits," Bachelor's Thesis, University of Arkansas, 2023.
[217] Lenovo, "Row Hammer Privilege Escalation," https://support.lenovo.com/us/en/product_security/row_hammer, 2015.
[218] Y. Levy *et al.*, "Logic Operations in Memory Using a Memristive Akers Array," *Microelectronics Journal*, 2014.
[219] D. Li *et al.*, "CyberRadar: A PUF-based Detecting and Mapping Framework for Physical Devices," arXiv:2201.07597, 2022.
[220] S. Li *et al.*, "DRISA: A DRAM-Based Reconfigurable In-Situ Accelerator," in *MICRO*, 2017.
[221] S. Li *et al.*, "Pinatubo: A Processing-in-Memory Architecture for Bulk Bitwise Operations in Emerging Non-Volatile Memories," in *DAC*, 2016.
[222] M. Lipp *et al.*, "Nethammer: Inducing Rowhammer Faults Through Network Requests," arXiv:1805.04956, 2018.
[223] Litex RowHammer Tester, "Payload Executor ISA considerations," https://github.com/antmicro/litex-rowhammer-tester/issues/6.
[224] J. Liu *et al.*, "An Experimental Study of Data Retention Behavior in Modern DRAM Devices," in *ISCA*, 2013.
[225] J. Liu *et al.*, "RAIDR: Retention-Aware Intelligent DRAM Refresh," in *ISCA*, 2012.
[226] L. Liu *et al.*, "Generating Robust DNN with Resistance to Bit-Flip based Adversarial Weight Attack," *IEEE TC*, 2022.
[227] Z. Liu *et al.*, "Concurrent Data Structures for Near-Memory Computing," in *SPAA*, 2017.
[228] S. Lloyd *et al.*, "In-memory Data Rearrangement for Irregular, Data-intensive Computing," *Computer*, 2015.
[229] S. Lloyd *et al.*, "Near Memory Key/Value Lookup Acceleration," in *MEMSYS*, 2017.
[230] S. Lloyd *et al.*, "Design Space Exploration of Near Memory Accelerators," in *MEMSYS*, 2018.
[231] K. Loughlin *et al.*, "Stop! Hammer Time: Rethinking Our Approach to Rowhammer Mitigations," in *HotOS*, 2021.
[232] K. Loughlin *et al.*, "MOESI-Prime: Preventing Coherence-Induced Hammering in Commodity Workloads," in *ISCA*, 2022.
[233] H. Luo *et al.*, "RowPress: Amplifying Read Disturbance in Modern DRAM Chips," in *ISCA*, 2023.
[234] H. Luo *et al.*, "CLR-DRAM: A Low-Cost DRAM Architecture Enabling Dynamic Capacity-Latency Trade-Off," in *ISCA*, 2020.
[235] M. Ma *et al.*, "Characterize the DRAM with FPGA," in *ICCSNT*, 2020.
[236] K. Mai *et al.*, "Smart Memories: A Modular Reconfigurable Architecture," in *ISCA*, 2000.
[237] J. A. Mandelman *et al.*, "Challenges and Future Directions for the Scaling of Dynamic Random-Access Memory (DRAM)," *IBM JRD*, 2002.
[238] N. Mansouri Ghiasi *et al.*, "GenStore: A High-Performance in-Storage Processing System for Genome Sequence Analysis," in *ASPLOS*, 2022.
[239] E. Manzhosov *et al.*, "Revisiting Residue Codes for Modern Memories," in *MICRO*, 2022.
[240] M. Marazzi *et al.*, "REGA: Scalable Rowhammer Mitigation with Refresh-Generating Activations," in *S&P*, 2022.
[241] M. Marazzi *et al.*, "ProTRR: Principled yet Optimal In-DRAM Target Row Refresh," in *S&P*, 2023.
[242] Maxwell, "FT20X User Manual," https://www.maxwell-fa.com/uploadfile/downloads/Maxwell-User%20manual(FT200%20LCD%20Controller).pdf.
[243] E. J. McCluskey, "Built-In Self-Test Structures," *IEEE Design & Test of Computers*, 1985.
[244] E. J. McCluskey, "Built-In Self-Test Techniques," *IEEE Design & Test of Computers*, 1985.
[245] mfactors, "JET-5612A Straight DDR4 DIMM Extender," https://mfactors.com/jet-5612a-straight-ddr4-dimm-extender/.

[246] Micron, "Mobile LPDDR3 SDRAM." [Online]. Available: http://www.micron.com/-/media/documents/products/data%20sheet/dram/mobile%20dram/low-power%20dram/lpddr3/253b_12-5x12-5_2ch_8-16gb_2c0f_mobile_lpddr3.pdf
[247] Micron, *Hybrid Memory Cube – HMC Gen2*, February 2018.
[248] Micron Technology, "TN-41-01: Calculating Memory System Power for DDR3," 2007.
[249] Micron Technology, "TN-40-07: Calculating Memory Power for DDR4 SDRAM," 2017.
[250] A. Morad *et al.*, "GP-SIMD Processing-in-Memory," *ACM TACO*, 2015.
[251] S. Mosanu *et al.*, "PiMulator: a Fast and Flexible Processing-in-Memory Emulation Platform," in *DATE*, 2022.
[252] T. Moscibroda *et al.*, "Memory Performance Attacks: Denial of Memory Service in Multi-Core Systems," in *USENIX Security*, 2007.
[253] R. C. Murphy *et al.*, "The Characterization of Data Intensive Memory Workloads on Distributed PIM Systems," in *Intelligent Memory Systems*. Springer, 2001.
[254] K. Mus *et al.*, "Jolt: Recovering TLS Signing Keys via Rowhammer Faults," *Cryptology ePrint Archive*, 2022.
[255] O. Mutlu, "Memory Scaling: A Systems Architecture Perspective," in *IMW*, 2013.
[256] O. Mutlu, "The RowHammer Problem and Other Issues We May Face as Memory Becomes Denser," in *DATE*, 2017.
[257] O. Mutlu, "RowHammer," https://people.inf.ethz.ch/omutlu/pub/onur-Rowhammer-TopPicksinHardwareEmbeddedSecurity-November-8-2018.pdf, 2018, Top Picks in Hardware and Embedded Security.
[258] O. Mutlu, "RowHammer and Beyond," in *COSADE*, 2019.
[259] O. Mutlu *et al.*, "RowHammer: A Retrospective," *IEEE TCAD Special Issue on Top Picks in Hardware and Embedded Security*, 2019.
[260] O. Mutlu *et al.*, "Stall-Time Fair Memory Access Scheduling for Chip Multiprocessors," in *MICRO*, 2007.
[261] O. Mutlu *et al.*, "Parallelism-Aware Batch Scheduling: Enhancing Both Performance and Fairness of Shared DRAM Systems," in *ISCA*, 2008.
[262] O. Mutlu *et al.*, "Fundamentally Understanding and Solving RowHammer," in *ASP-DAC*, 2023.
[263] O. Mutlu *et al.*, "Research Problems and Opportunities in Memory Systems," *SUPERFRI*, 2014.
[264] L. Nai *et al.*, "GraphPIM: Enabling Instruction-level Pim Offloading in Graph Computing Frameworks," in *HPCA*, 2017.
[265] R. Nair, "Evolution of Memory Architecture," *Proceedings of the IEEE*, 2015.
[266] R. Nair *et al.*, "Active Memory Cube: A Processing-in-Memory Architecture for Exascale Systems," *IBM JRD*, 2015.
[267] A. Naseredini *et al.*, "ALARM: Active LeArning of Rowhammer Mitigations," https://users.sussex.ac.uk/~mfb21/rh-draft.pdf, 2022.
[268] Nickel Electronics, "DRAM Memory Testing," https://www.nickelelectronics.com/memory-testing/.
[269] A. Olgun *et al.*, "Sectored DRAM: An Energy-Efficient High-Throughput and Practical Fine-Grained DRAM Architecture," arXiv:2207.13795, 2022.
[270] A. Olgun *et al.*, "PiDRAM: A Holistic End-to-end FPGA-based Framework for Processing-in-DRAM," *TACO*, 2022.
[271] A. Olgun *et al.*, "An Experimental Analysis of RowHammer in HBM2 DRAM Chips," in *DSN Disrupt*, 2023.
[272] A. Olgun *et al.*, "QUAC-TRNG: High-Throughput True Random Number Generation Using Quadruple Row Activation in Commodity DRAM Chips," in *ISCA*, 2021.
[273] G. F. Oliveira *et al.*, "DAMOV: A New Methodology and Benchmark Suite for Evaluating Data Movement Bottlenecks," *IEEE Access*, 2021.
[274] G. F. Oliveira *et al.*, "A New Methodology and Open-Source Benchmark Suite for Evaluating Data Movement Bottlenecks: A Near-Data Processing Case Study," in *SIGMETRICS*, 2021.
[275] L. Orosa *et al.*, "SpyHammer: Using RowHammer to Remotely Spy on Temperature," arXiv:2210.04084, 2022.
[276] L. Orosa *et al.*, "CODIC: A Low-Cost Substrate for Enabling Custom In-DRAM Functionalities and Optimizations," in *ISCA*, 2021.
[277] L. Orosa *et al.*, "A Deeper Look into RowHammer's Sensitivities: Experimental Analysis of Real DRAM Chips and Implications on Future Attacks and Defenses," in *MICRO*, 2021.
[278] M. Oskin *et al.*, "Active Pages: A Computation Model for Intelligent Memory," in *ISCA*, 1998.
[279] J. H. Park *et al.*, "RowHammer Reduction Using a Buried Insulator in a Buried Channel Array Transistor," *IEEE Transactions on Electron Devices*, 2022.
[280] Y. Park *et al.*, "Graphene: Strong yet Lightweight Row Hammer Protection," in *MICRO*, 2020.
[281] M. Patel *et al.*, "Bit-Exact ECC Recovery (BEER): Determining DRAM On-Die ECC Functions by Exploiting DRAM Data Retention Characteristics," in *MICRO*, 2020.
[282] M. Patel *et al.*, "Understanding and Modeling On-Die Error Correction in Modern DRAM: An Experimental Study Using Real Devices," in *DSN*, 2019.
[283] M. Patel *et al.*, "The Reach Profiler (REAPER): Enabling the Mitigation of DRAM Retention Failures via Profiling at Aggressive Conditions," in *ISCA*, 2017.
[284] D. Patterson *et al.*, "A Case for Intelligent RAM," *IEEE Micro*, 1997.
[285] A. Pattnaik *et al.*, "Scheduling Techniques for GPU Architectures with Processing-in-Memory Capabilities," in *PACT*, 2016.
[286] PCI-SIG, *PCI Express Base Specification Revision 3.0*, November 2010.
[287] P. Pessl *et al.*, "DRAMA: Exploiting DRAM Addressing for Cross-CPU Attacks," in *USENIX Security*, 2016.
[288] D. Poddebniak *et al.*, "Attacking Deterministic Signature Schemes using Fault Attacks," in *EuroS&P*, 2018.
[289] S. H. Pugsley *et al.*, "NDC: Analyzing the Impact of 3D-stacked Memory+ Logic Devices on MapReduce Workloads," in *ISPASS*, 2014.
[290] pybind, "pybind11 — GitHub Repository," https://github.com/pybind/pybind11, 2022.
[291] R. Qiao *et al.*, "A New Approach for RowHammer Attacks," in *HOST*, 2016.
[292] B. Querbach *et al.*, "A Reusable BIST with Software Assisted Repair Technology for Improved Memory and IO Debug, Validation and Test Time," in *ITC*, 2014.
[293] B. Querbach *et al.*, "Architecture of a Reusable BIST Engine for Detection and Auto Correction of Memory Failures and for IO Debug, Validation, Link Training, and Power Optimization on 14nm SOC," *IEEE D&T*, 2016.
[294] M. Qureshi *et al.*, "AVATAR: A Variable-Retention-Time (VRT) Aware Refresh for DRAM Systems," in *DSN*, 2015.
[295] M. Qureshi *et al.*, "Hydra: Enabling Low-Overhead Mitigation of Row-Hammer at Ultra-Low Thresholds via Hybrid Tracking," in *ISCA*, 2022.
[296] A. S. Rakin *et al.*, "DeepSteal: Advanced Model Extractions Leveraging Efficient Weight Stealing in Memories," in *S&P*, 2022.
[297] K. Razavi *et al.*, "Flip Feng Shui: Hammering a Needle in the Software Stack," in *USENIX Security*, 2016.
[298] S. H. S. Rezaei *et al.*, "NoM: Network-on-Memory for Inter-Bank Data Transfer in Highly-Banked Memories," *CAL*, 2020.
[299] A. Rodrigues *et al.*, "Towards a Scatter-Gather Architecture: Hardware and Software Issues," in *MEMSYS*, 2019.
[300] A. Roohi *et al.*, "Efficient Targeted Bit-Flip Attack Against the Local Binary Pattern Network," in *HOST*, 2022.
[301] RS, "RS PRO Type K Thermocouple," https://docs.rs-online.com/9b34/A700000007350702.pdf.
[302] SAFARI Research Group, "DRAM-Bender — GitHub Repository," https://github.com/CMU-SAFARI/DRAM-Bender.
[303] SAFARI Research Group, "QUAC-TRNG — GitHub Repository," https://github.com/CMU-SAFARI/QUAC-TRNG.
[304] SAFARI Research Group, "U-TRR — GitHub Repository," https://github.com/CMU-SAFARI/U-TRR.
[305] SAFARI Research Group, "RowHammer — GitHub Repository," https://github.com/CMU-SAFARI/rowhammer, 2014.
[306] SAFARI Research Group, "SoftMC — GitHub Repository," https://github.com/CMU-SAFARI/softmc, 2017.
[307] G. Saileshwar *et al.*, "Randomized Row-Swap: Mitigating Row Hammer by Breaking Spatial Correlation Between Aggressor and Victim Rows," in *ASPLOS*, 2022.
[308] P. C. Santos *et al.*, "Operand Size Reconfiguration for Big Data Processing in Memory," in *DATE*, 2017.
[309] S. Saroiu *et al.*, "How to Configure Row-Sampling-Based Rowhammer Defenses," *DRAMSec*, 2022.
[310] S. Saroiu *et al.*, "The Price of Secrecy: How Hiding Internal DRAM Topologies Hurts Rowhammer Defenses," in *IRPS*, 2022.
[311] A. Saxena *et al.*, "AQUA: Scalable Rowhammer Mitigation by Quarantining Aggressor Rows at Runtime," in *MICRO*, 2022.
[312] M. Seaborn *et al.*, "Exploiting the DRAM Rowhammer Bug to Gain Kernel Privileges," http://googleprojectzero.blogspot.com.tr/2015/03/exploiting-dram-rowhammer-bug-to-gain.html, 2015.
[313] M. Seaborn *et al.*, "Exploiting the DRAM Rowhammer Bug to Gain Kernel Privileges," *Black Hat*, 2015.
[314] V. Seshadri *et al.*, "Buddy-RAM: Improving the Performance and Efficiency of Bulk Bitwise Operations Using DRAM," arXiv:1611.09988, 2016.
[315] V. Seshadri *et al.*, "Fast Bulk Bitwise AND and OR in DRAM," *IEEE CAL*, 2015.
[316] V. Seshadri *et al.*, "RowClone: Fast and Energy-Efficient In-DRAM Bulk Data Copy and Initialization," in *MICRO*, 2013.
[317] V. Seshadri *et al.*, "Ambit: In-memory Accelerator for Bulk Bitwise Operations using Commodity DRAM Technology," in *MICRO*, 2017.
[318] V. Seshadri *et al.*, "Gather-Scatter DRAM: In-DRAM Address Translation to Improve the Spatial Locality of Non-Unit Strided Accesses," in *MICRO*, 2015.
[319] V. Seshadri *et al.*, "Simple Operations in Memory to Reduce Data Movement," in *Advances in Computers, Volume 106*, 2017.
[320] V. Seshadri *et al.*, "In-DRAM Bulk Bitwise Execution Engine," arXiv:1905.09822, 2019.
[321] S. M. Seyedzadeh *et al.*, "Mitigating Wordline Crosstalk Using Adaptive Trees of Counters," in *ISCA*, 2018.
[322] A. Shafiee *et al.*, "ISAAC: A Convolutional Neural Network Accelerator with in-situ Analog Arithmetic in Crossbars," *ISCA*, 2016.
[323] S. Sharma *et al.*, "A Review on Study of Defects of DRAM-RowHammer and Its Mitigation," *Journal For Basic Sciences*, 2022.
[324] D. E. Shaw *et al.*, "The NON-VON Database Machine: A Brief Overview," *IEEE Database Eng. Bull.*, 1981.
[325] H. Shin *et al.*, "McDRAM: Low latency and energy-efficient matrix computations in DRAM," *IEEE TCADICS*, 2018.
[326] G. Singh *et al.*, "FPGA-based Near-Memory Acceleration of Modern Data-Intensive Applications," *IEEE Micro*, 2021.
[327] G. Singh *et al.*, "NAPEL: Near-Memory Computing Application Performance Prediction via Ensemble Learning," *DAC*, 2019.
[328] G. Singh *et al.*, "Accelerating Weather Prediction using Near-Memory Reconfigurable Fabric," *ACM TRETS*, 2021.
[329] G. Singh *et al.*, "NERO: A Near High-Bandwidth Memory Stencil Accelerator for Weather Prediction Modeling," in *FPL*, 2020.
[330] M. Son *et al.*, "Making DRAM Stronger Against Row Hammering," in *DAC*, 2017.
[331] Y. H. Son *et al.*, "Reducing Memory Access Latency with Asymmetric DRAM Bank Organizations," in *ISCA*, 2013.
[332] F. Staudigl *et al.*, "NeuroHammer: Inducing Bit-Flips in Memristive Crossbar Memories," in *DATE*, 2022.
[333] A. Steininger, "Testing and Built-In Self-Test – A Survey," *Journal of Systems Architecture*, 2000.
[334] H. S. Stone, "A Logic-in-Memory Computer," *IEEE TC*, 1970.
[335] L. Subramanian *et al.*, "The Blacklisting Memory Scheduler: Achieving High Performance and Fairness at Low Cost," in *ICCD*, 2014.
[336] Z. Sura *et al.*, "Data Access Optimization in a Processing-in-memory System," in *CF*, 2015.
[337] S. Sutar *et al.*, "D-PUF: An Intrinsically Reconfigurable DRAM PUF for Device Authentication and Random Number Generation," in *TECS*, 2018.
[338] A. Tatar *et al.*, "Defeating Software Mitigations Against Rowhammer: A Surgical Precision Hammer," in *RAID*, 2018.

[339] A. Tatar *et al.*, "Throwhammer: Rowhammer Attacks Over the Network and Defenses," in *USENIX ATC*, 2018.
[340] Teradyne, "Magnum Memory Test System," http://www.teradyne.com/products/semiconductor-test/magnum.
[341] The Pandas Development Team, "Pandas," https://doi.org/10.5281/zenodo.3509134, 2020.
[342] Y. Tobah *et al.*, "SpecHammer: Combining Spectre and Rowhammer for New Speculative Attacks," in *S&P*, 2022.
[343] M. C. Tol *et al.*, "Toward Realistic Backdoor Injection Attacks on DNNs using RowHammer," arXiv:2110.07683, 2022.
[344] C. Tomita *et al.*, "Extracting the secrets of openssl with rambleed," *Sensors*, 2022.
[345] V. van der Veen *et al.*, "Drammer: Deterministic Rowhammer Attacks on Mobile Platforms," in *CCS*, 2016.
[346] V. van der Veen *et al.*, "GuardION: Practical Mitigation of DMA-Based Rowhammer Attacks on ARM," in *DIMVA*, 2018.
[347] R. K. Venkatesan *et al.*, "Retention-Aware Placement in DRAM (RAPID): Software Methods for Quasi-Non-Volatile DRAM," in *HPCA*, 2006.
[348] S. Vig *et al.*, "Rapid Detection of Rowhammer Attacks Using Dynamic Skewed Hash Tree," in *HASP*, 2018.
[349] T. Vogelsang, "Understanding the Energy Consumption of Dynamic Random Access Memories," in *MICRO*, 2010.
[350] A. J. Walker *et al.*, "On DRAM RowHammer and the Physics on Insecurity," *IEEE TED*, 2021.
[351] J. Wang *et al.*, "Research and Implementation of Rowhammer Attack Method based on Domestic NeoKylin Operating System," in *ICFTIC*, 2022.
[352] Y. Wang *et al.*, "Reducing DRAM Latency via Charge-Level-Aware Look-Ahead Partial Restoration," in *MICRO*, 2018.
[353] Y. Wang *et al.*, "FIGARO: Improving System Performance via Fine-Grained In-DRAM Data Relocation and Caching," in *MICRO*, 2020.
[354] M. L. Waskom, "Seaborn: Statistical Data Visualization," *Journal of Open Source Software*, 2021.
[355] Z. Weissman *et al.*, "JackHammer: Efficient Rowhammer on Heterogeneous FPGA–CPU Platforms," arXiv:1912.11523, 2020.
[356] M. Wi *et al.*, "SHADOW: Preventing Row Hammer in DRAM with Intra-Subarray Row Shuffling," in *HPCA*. IEEE, 2023.
[357] J. Woo *et al.*, "Scalable and Secure Row-Swap: Efficient and Safe Row Hammer Mitigation in Memory Systems," in *HPCA*, 2023.
[358] Y. Xi *et al.*, "In-Memory Learning With Analog Resistive Switching Memory: A Review and Perspective," *Proceedings of the IEEE*, 2020.
[359] Y. Xiao *et al.*, "One Bit Flips, One Cloud Flops: Cross-VM Row Hammer Attacks and Privilege Escalation," in *USENIX Security*, 2016.
[360] L. Xie *et al.*, "Fast Boolean Logic Papped on Memristor Crossbar," in *ICCD*, 2015.
[361] Xilinx, "Virtex-6 FPGA Memory Interface Solutions," http://www.xilinx.com/support/documentation/ip_documentation/mig/v3_92/ug406.pdf.
[362] Xilinx, "Xilinx Zynq-7000 SoC ZC706 Evaluation Kit," https://www.xilinx.com/products/boards-and-kits/ek-z7-zc706-g.html.
[363] Xilinx, *7 Series FPGAs Memory Interface Solutions*, March 2011.
[364] Xilinx, *Virtex-6 FPGA Integrated Block for PCI Express*, Mar. 2011.
[365] Xilinx, *ML605 Hardware User Guide*, Oct. 2012.
[366] Xilinx, *ISE Design Suite 14: Release Notes, Installation, and Licensing*, July 2020.
[367] Xilinx, *Vivado Design Suite User Guide: Logic Simulation*, November 2020.
[368] Xilinx, *AXI High Bandwidth Memory Controller v1.0*, 2021.
[369] Xilinx, *DMA/Bridge Subsystem for PCI Express v4.1*, April 2021.
[370] Xilinx, *UltraScale Architecture-Based FPGAs Memory IP v1.4*, June 2021.
[371] Xilinx Inc., "Xilinx Alveo U200 FPGA Board," https://www.xilinx.com/products/boards-and-kits/alveo/u200.html.
[372] X. Xin *et al.*, "ELP2IM: Efficient and Low Power Bitwise Operation Processing in DRAM," in *HPCA*, 2020.
[373] A. G. Yağlıkcı *et al.*, "Security Analysis of the Silver Bullet Technique for RowHammer Prevention," arXiv:2106.07084, 2021.
[374] A. G. Yağlıkcı *et al.*, "Understanding RowHammer Under Reduced Wordline Voltage: An Experimental Study Using Real DRAM Devices," in *DSN*, 2022.
[375] A. G. Yağlıkcı *et al.*, "HiRA: Hidden Row Activation for Reducing Refresh Latency of Off-the-Shelf DRAM Chips," in *MICRO*, 2022.
[376] A. G. Yağlıkcı *et al.*, "BlockHammer: Preventing RowHammer at Low Cost by Blacklisting Rapidly-Accessed DRAM Rows," in *HPCA*, 2021.
[377] C. Yang *et al.*, "A Hybrid Built-In Self-Test Scheme for DRAMs," in *VLSI-DAT*, 2015.
[378] L.-H. Yang *et al.*, "Socially-Aware Collaborative Defense System against Bit-Flip Attack in Social Internet of Things and Its Online Assignment Optimization," in *ICCCN*, 2022.
[379] F. Yao *et al.*, "Deephammer: Depleting the Intelligence of Deep Neural Networks Through Targeted Chain of Bit Flips," in *USENIX Security*, 2020.
[380] L. Yavits *et al.*, "GIRAF: General Purpose In-Storage Resistive Associative Framework," *IEEE TPDS*, 2021.
[381] J. M. You *et al.*, "MRLoc: Mitigating Row-Hammering Based on Memory Locality," in *DAC*, 2019.
[382] Y. You *et al.*, "A Self-Testing Dynamic RAM Chip," *TED*, 1985.
[383] J. Yu *et al.*, "Memristive Devices for Computation-in-Memory," in *DATE*, 2018.
[384] Y. Zha *et al.*, "Hyper-AP: Enhancing Associative Processing Through A Full-Stack Optimization," in *ISCA*, 2020.
[385] D. P. Zhang *et al.*, "TOP-PIM: Throughput-Oriented Programmable Processing in Memory," in *HPDC*, 2014.
[386] J. Zhang *et al.*, "MEG: A RISCV-based System Emulation Infrastructure for Near-data Processing Using FPGAs and High-bandwidth Memory," *TRETS*, 2020.
[387] M. Zhang *et al.*, "GraphP: Reducing Communication for PIM-based Graph Processing with Efficient Data Partition," in *HPCA*, 2018.
[388] T. Zhang *et al.*, "Half-DRAM: A High-Bandwidth and Low-Power DRAM Architecture from the Rethinking of Fine-Grained Activation," in *ISCA*, 2014.
[389] Z. Zhang *et al.*, "Triggering Rowhammer Hardware Faults on ARM: A Revisit," in *ASHES*, 2018.
[390] Z. Zhang *et al.*, "Leveraging EM Side-Channel Information to Detect Rowhammer Attacks," in *S&P*, 2020.
[391] Z. Zhang *et al.*, "PTHammer: Cross-User-Kernel-Boundary Rowhammer Through Implicit Accesses," in *MICRO*, 2020.
[392] Z. Zhang *et al.*, "SoftTRR: Protect Page Tables against Rowhammer Attacks using Software-only Target Row Refresh," in *USENIX ATC*, 2022.
[393] Z. Zhang *et al.*, "Implicit Hammer: Cross-Privilege-Boundary Rowhammer through Implicit Accesses," *IEEE TDSC*, 2022.
[394] L. Zheng *et al.*, "RRAM-based TCAMs for pattern search," in *ISCAS*, 2016.
[395] M. Zheng *et al.*, "TrojViT: Trojan Insertion in Vision Transformers," arXiv:2208.13049, 2022.
[396] R. Zhou *et al.*, "LT-PIM: An LUT-Based Processing-in-DRAM Architecture With RowHammer Self-Tracking," *IEEE CAL*, 2022.
[397] Q. Zhu *et al.*, "Accelerating Sparse Matrix-matrix Multiplication with 3D-stacked Logic-in-memory Hardware," in *HPEC*, 2013.
[398] Y. Zhuo *et al.*, "GraphQ: Scalable PIM-based Graph Processing," in *MICRO*, 2019.
[399] V. Zois *et al.*, "Massively Parallel Skyline Computation for Processing-in-Memory Architectures," in *PACT*, 2018.